

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
29 August 2002 (29.08.2002)

PCT

(10) International Publication Number
WO 02/067273 A1

(51) International Patent Classification⁷: **H01B 1/12**, 1/20,
C08G 75/00, H01L 23/14

(21) International Application Number: PCT/US02/04679

(22) International Filing Date: 15 February 2002 (15.02.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:

60/269,606	16 February 2001 (16.02.2001)	US
60/298,174	13 June 2001 (13.06.2001)	US
09/999,171	30 November 2001 (30.11.2001)	US

(63) Related by continuation (CON) or continuation-in-part
(CIP) to earlier application:

US	Not furnished (CIP)
Filed on	Not furnished

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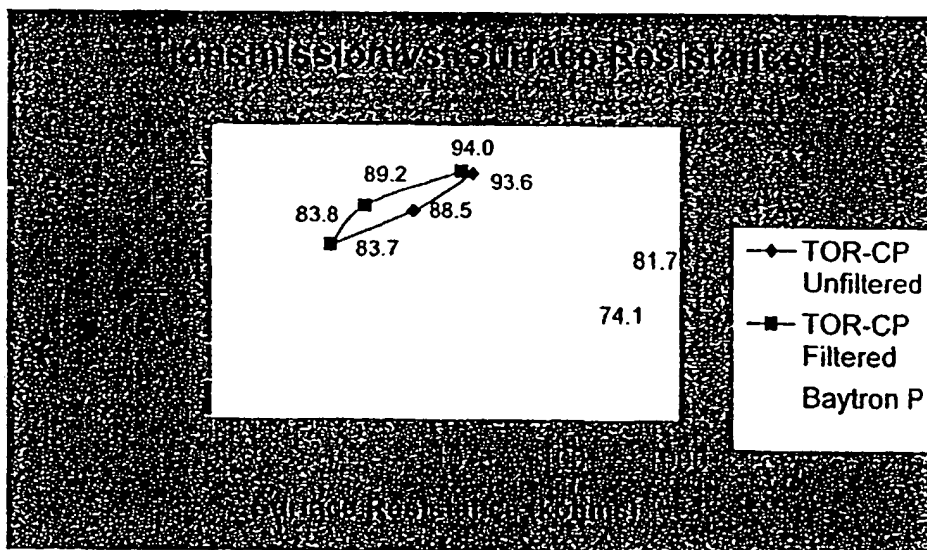
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(81) Designated States (national): AE, AG, AL, AM, AT, AU,
AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU,
CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH,
GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC,
LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW,
MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG,
SI, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ,
VN, YU, ZA, ZM, ZW.

(84) Designated States (regional): ARIPO patent (GH, GM,
KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW),
Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR,

[Continued on next page]

(54) Title: COMPOSITIONS PRODUCED BY SOLVENT EXCHANGE METHODS AND USES THEREOF



(57) Abstract: Disclosed are compositions formed by a method for exchanging solvent in a mixture that includes water and an optionally substituted thiophene. Also disclosed are methods for making and using such compositions.

WO 02/067273 A1

WO 02/067273 A1



GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent
(BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR,
NE, SN, TD, TG).

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

Published:

— *with international search report*

5 **COMPOSITIONS PRODUCED BY SOLVENT EXCHANGE**
 METHODS AND USES THEREOF

CROSS-REFERENCE TO RELATED APPLICATIONS

 The present application claims benefit to U.S Patent Application No.
10 09/999,171 filed on November 30, 2001 which application claims benefit to U.S.
Provisional Application No. 60/298,174 as filed on June 13, 2001, which application
claims benefit to U.S. Provisional Application No. 60/269,606 as filed on February
16, 2001. The disclosures of the USSN Nos. 09/999,171; 60/298,174 and 60/269,606
applications are each incorporated herein by reference.

15

FIELD OF THE INVENTION

 The present invention generally relates to compositions produced from solvent
exchange processes. In general, the processes replace water in a thiophene mixture
with at least one other solvent. A preferred thiophene mixture is a water saturated
20 Baytron™ formulation. Also provided are useful articles including organic solvent
based polymeric coatings as well as methods for making and using same.

BACKGROUND OF THE INVENTION

 There is increasing recognition that performance of a wide spectrum of
25 electronic and optical articles can be enhanced by including a conductive molecule.
Examples of such articles include anti-static coatings, films, as well as a variety of
electronic implementations. See generally *Handbook on Conducting Polymers*
(Skotheim, T. J. ed.) (Dekker, New York, 1986).

30 Many types of conductive organic molecules have been reported. For
example, U.S. Pat. Nos. 6,172,591; 4,237,441; and 5,378,407 disclose organic
polymers with a carbon black or metallic conductive filler.

 Organic polymers that are intrinsically conductive have attracted substantial
35 interest. Generally, such polymers include sp^2 hybridized carbon atoms that have (or
can be adapted to have) delocalized electrons for storing and communicating

electronic charge. Some polymers are thought to have conductivities neighboring those traditional silicon-based and metallic conductors. These and other performance characteristics make such conductive polymers desirable for a wide range of applications. See Burroughes, J.H. et al. (1986) *Nature* 335:137; Sirringhaus, H. et al. (2000) *Science*, 290, 2123; Sirringhaus, H. et al. (1999) *Nature* 401: 2; and references cited therein, for example.

Other conductive polymers have been reported. These polymers include a many optionally substituted polypyrrole, polyaniline, polyacetylene, and polythiophene compounds. See EP-A 302 304; EP-A 440 957; DE OS 4 211 459; U.S. Pat. Nos. 6,083,635 and 6,084,040; and Burroughes, J.H., *supra*.

There is recognition that many conductive polymers can be used to coat a wide range of synthetic or natural articles such as those made from glass, plastic, wood and fibers to provide an electrostatic or anti-static coating. Typical coatings can be applied as sprays, powders and the like using recognized coating or printing processes.

However there is increasing understanding that many prior conductive polymers are not useful for all intended applications.

For example, many of such polymers are not sufficiently conductive or transparent for many applications. In particular, many suffer from unacceptable conductivity, poor stability, and difficult processing requirements. Other shortcomings have been reported. See e.g, the U.S. Pat. Nos. 6,084,040 and 6,083,635.

There have been attempts to improve some of the prior conductive polymers.

For example, a particular 3,4-polyethylene dioxythiophene (commercially available as Baytron™ P) has been reported to offer good conductivity, transparency, stability, hydrolysis resistance and processing characteristics. See Bayer AG product literature (Edition 10/97; Order No. Al 5593) Inorganics Business Group D-51368, Leverkusen, Germany.

More specific Baytron™ formulations have been reported for use in specific applications. Illustrative formulations (P type) include CPUD2, CPP103T, CPP105T, CPP116.6, CPP134.18, CP135, CPP 4531 I, CPP 4531 E3 and CPG 130.6. Baytron™
5 M is reported to be a monomer of poly(3,4-ethylenedioxythiophene) and it has been reported to be useful in the manufacture of organic conductive polymers. Further information relating to using Baytron™ formulations can be obtained from the Bayer Corporation, 100 Bayer Rd. Pittsburgh, PA 15205-9741. See also the Bayer Corporation website at bayerus.com the disclosure of which is incorporated by
10 reference.

Unfortunately, use of many prior mono- and polythiophene formulations has been problematic.

15 For example, many important Baytron™ formulations are provided with significant amounts of water solvent. In particular, many Baytron™ P formulations are available as water-saturated colloidal dispersions of the conductive polymer. Typically, a suitable counter ion such as polystyrene sulfonic acid (PSS) is added to the dispersion. There is increasing recognition that many, if not all, Baytron™
20 formulations would be more useful if means existed for exchanging the water solvent with one or more other solvents of choice.

There have been limited attempts to develop such solvent exchange methods. Nearly all of the attempts have relied on traditional liquid fractionation and distillation
25 schemes. Such approaches have not been able to exchange the solvent for the water in a way that is effective and reproducible.

Flexible electronic device "writing" or "printing" has attracted much recent attention. An example of such a technique involves dispersing an aqueous and
30 conductive thiophene preparation with an ink-jet printer. Typically, poly(3,4-ethylenedioxythiophene) doped with polystyrene sulfonic acid (PEDOT/PSS) is employed. See generally Dagni, R. in *Chemistry and Engineering*, January 1, 2001, pp. 26-27 as well as references cited therein.

However, these writing or printing procedures have suffered for want of an effective and reproducible means of replacing the water with more useful exchange solvents.

5

There is recognition that many electro-optic devices, such as light emitting diodes (LED's) and photovoltaic cells, require electrically conductive and optically transparent films/coatings as electrode materials. Presently, transparent electrodes in electro-optic devices are made of indium doped tin oxide (ITO) coated glass

10 substrates.

However, most prior ITO layers have suffered from shortcomings.

For example, most prior manufacturing processes involving ITO are
15 cumbersome and costly to perform. An illustration is the need to conduct vacuum deposition in a controlled gas atmosphere. Furthermore, most prior ITO films are brittle, difficult to prepare and manipulate, particularly when used in film formats on large area substrates or flexible substrates. See generally Y. Cao, et al. in *Conjugated Polymeric Materials: Opportunities in Electronics, Optoelectronics and Molecular*
20 *Electronics*, NATO Advanced Study Institute, Series E: Applied Sciences, J. L. Bredas and R. R. Chance, Eds., Vol. 82, Kluwer Academic, Holland (1990). See also US Pat. No. 5,618,469 and EPO Patent 686,662.

There is belief that certain conducting polymers and coatings may be qualified
25 for some organic light emitting diode (OLED) applications. Briefly, OLEDs are display compositions based on sandwiching deposited organic molecules or polymers between two electrodes. Light emission or luminescence occurs when charged carriers associate with the electrodes recombine and emit light. See US Pat. No. 5,904,961, for instance.

30

More specifically, a typical OLED includes a metal cathode, electrode transport layer (ETL), organic emitters, the HIL, an ITO anode and glass substrate. Light output passes through the glass substrate.

Electrically conductive and optically transparent coatings have been made with polyaniline (PANI) (U.S. Patent No. 5618469) and PEDOT/PSS polymer dispersion (Eur Patent 686662).

5 However, many of the prior coatings have recognized drawbacks particularly in relation to OLED applications.

As an example, many have limitations in manufacturing practical electro-optic devices. In particular, it is well known that many PANI systems are not stable.

10 Performance degrades over time. Although there is some understanding that performance of PEDOT:PSS-based devices are stable, many prior PEDOT/PSS polymers are aqueous based. Fabricating PEDOT:PSS coatings onto ITO coated substrates requires cumbersome manufacturing processes. Further, the hydrophilic nature of the PEDOT:PSS system attracts moisture, even through the protective

15 moisture barrier. This characteristic has several disadvantages including premature failure during use.

It would be desirable to have coating and related compositions that are easy to make and use. It would be especially desirable to have solvent-exchanged

20 PEDOT:PSS compositions as well as methods for making and using same that exhibit low resistivity and are suitable for OLED use.

SUMMARY OF THE INVENTION

The present invention relates to solvent exchange methods for replacing water

25 in a thiophene mixture. Preferred methods of the invention replace some or all of the water with at least one other solvent. Preferably, the thiophene mixture is a Baytron™ formulation. Also provided are compositions produced by the methods as well as useful articles that include or consist of such compositions. The invention has a wide spectrum of important applications including providing converted (solvent

30 exchanged) Baytron™ formulations for use in consumer goods and electronic writing techniques.

As discussed, it has been difficult to replace the water associated with many thiophene mixtures, particularly but not exclusively, mono- and polythiophene mixtures known as Baytron™ formulations. Such formulations are often provided as colloidal or water saturated materials. The present invention addresses this need eg.,
5 by providing methods for replacing (exchanging) the water with at least one other more desirable solvent. Significantly, the present methods can be controlled by an invention user so that all or part of the water in mixture is exchanged as needed. Also significantly, the invention can be practiced using standard laboratory equipment, thereby making the invention cost effective in most embodiments. Preferred use of
10 the invention expands the usefulness of thiophene mixtures, particularly the Baytron™ formulations, into applications that heretofore have been difficult or impossible to practice.

The present invention also relates to compositions, preferably polymer
15 coatings, that are easy to make and use. Typically, such compositions are relatively stable and involve use of non- or low toxicity solvents. Preferred compositions according to the invention are PEDOT:PSS compositions, more preferably solvent-exchanged PEDOT:PSS coating compositions suitable for use in a range of electro-optical implemenations including OLEDs.

20

Such compositions provide advantages including good conductivity, high optical tranparency and environmental stability. Significantly, preferred compositions of the invention can be used to replace indium doped tin oxide (ITO) coated glass substrates that are part of many standard OLEDs.

25

Also encompassed by the invention are methods for making and using the present compositions. In one embodiment, the methods involve subjecting PEDOT:PSS compositions to conditions that decrease resistivity when compared to (control) compositions not receiving such treatment. Preferred conditions generally
30 involve at least one drying treatment. Also disclosed are methods for making such compositions in which at least one of the method steps involves drying treatment. By the phrase "drying treatment" is meant exposure to at least one condition that causes,

either directly or indirectly, loss of solvent from the composition, preferably exchanged solvent.

The drying treatments provided by the invention provide substantial
5 advantages. In particular, practice of such treatment steps in the methods of the invention provide a straightforward and cost effective way of improving composition performance by assisting solvent loss. Preferred practice involves subjecting
conductive coatings of the invention to ambient air and/or heat treatment to help
remove solvent, and has been discovered, to help improve performance characteristics
10 such as resistivity. Significantly, such drying treatments are compatible with most manufacturing processes and can be scaled-up as needed. More specific information about the drying treatments is provided in the discussion and examples following.

The invention also features electro-optical implementations that include at
15 least one of the compositions disclosed herein including preferred PEDOT:PSS compositions. An illustration of such an implementation is an OLED or related device. Such OLEDs reduce or avoid use of hard-to-manipulate ITO components while providing coatings with improved performance features, especially resistivity. As provided below, it is an object of the invention to replace prior ITO components
20 with at least one of the compositions of this invention provided as an OLED hole injection layer (HIL).

Accordingly, and in one aspect, the invention provides methods for
exchanging (in whole or in part) the water present in a thiophene mixture with at least
25 one other solvent. A preferred mixture includes at least one thiophene, preferably an optionally substituted mono- or polythiophene, more preferably a water saturated Baytron™ formulation. In one embodiment, the method includes at least one and preferably all of the following steps:

- 30 a) heating at least one solvent in a vessel under conditions suitable for vaporizing water,
- b) contacting the heated solvent with the thiophene mixture (comprising the water and at least one optionally substituted mono- or polythiophene), which contact is sufficient to remove at least part of the water from the mixture as vapor; and

c) exchanging the water removed from the mixture with the solvent.

Preferred practice of the invention involves heating the solvent before contact with the thiophene mixture, although in some invention embodiments substantially contemporaneous solvent heating may be desirable. Preferred heating conditions favor production of water vapor from the mixture. Without wishing to be bound to theory, it is believed that heating the solvent before the contact helps to reduce prolonged contact between the thiophene mixture and the exchange solvent. Such limited contact has many benefits including enhancing water loss from the mixture and increasing exchange with the heated solvent. In contrast, prior practice has been limited to more traditional distillation schemes featuring gradual liquid heating and close solution contact. These schemes are not always designed to minimize contact between the exchanging solvent and the thiophene mixture. Such limited contact is also believed to reduce or avoid binding potential (covalent and non-covalent) between the water and exchange solvent. Such binding is believed to have impeded many past attempts to reduce the amount of or eliminate water from some thiophene mixtures. As will become more apparent from the following discussion, these and other features of the invention provide for more efficient solvent exchange than has heretofore been possible, particularly with many Baytron™ formulations.

20

Additionally preferred practice of the invention involves maximizing the contact area of the heated solvent with respect to the contact area of the thiophene mixture. Without wishing to be bound to any theory, it is believed that by increasing the heated solvent contact area relative to that of the thiophene mixture, it is possible to boost heat transfer from the exchange solvent to the mixture. In this invention example, the relatively large heated solvent contact area helps to transfer heat quickly and efficiently from the exchange solvent to the mixture. This invention feature also helps to achieve an invention objective ie, the reduction or elimination of unwanted binding between the water and exchange solvent.

25
30

The invention provides many other important advantages.

For example, in another aspect, the invention provides highly useful compositions that include or consist of at least one of the converted (solvent

exchanged) thiophene mixtures. A preferred converted thiophene mixture is derived from an optionally substituted mono- or polythiophene, particularly a Baytron™ formulation in which the water solvent has been totally or partially replaced with at least one other solvent. In this invention embodiment, it has been found that such

5 converted thiophene mixtures feature better electrical conductivity than corresponding unconverted (control) mixtures. Significantly, such better conductivity is achieved with films and coatings having less thickness than conventional films and coatings made from many Baytron™ formulations. Without wishing to be bound to theory, preferred practice of the invention is believed to provide for more conductive polymer

10 chain orientations. This and other features of the invention will help expand the use of the Baytron™ formulations into a variety of applications in which good conductivity and minimal film or coating thickness is desired. It has also been found that converted thiophene mixtures of the invention feature improved stability to air and moisture compared to corresponding unconverted (control) mixtures.

15

Turning to the invention methods, it will be understood that it is possible to increase the contact area of the heated solvent by one or a combination of strategies.

For example, in one embodiment, the foregoing solvent exchange method

20 further includes adding about 1 unit volume of the thiophene mixture to more than about one unit volume of the heated solvent e.g., at least about 2 unit volumes of the heated solvent per unit volume of the mixture. The larger heated solvent volume provides the relatively large heated solvent contact area to move heat effectively from the exchange solvent to thiophene mixture.

25

The heated solvent, thiophene mixture (or both), can be provided in forms so that the heated solvent has a relatively large contact area when compared to the mixture. As an example, the contacting step of the methods can be adapted to include adding the thiophene mixture to the vessel as a flow stream, mist, aerosol; or a

30 combination thereof having the larger contact area.

Typically, but not exclusively, the heated exchange solvent is provided as a pool in the vessel which pool has the relatively larger contact area relative to the

added mixture. Addition of that mixture to the vessel can be continuous or discontinuous as needed e.g., as a semi-continuous flow stream or as drops of the mixture added to the pool of heated solvent. In another example, the contacting step of the method includes dispersing the mixture along the surface of the heated solvent.

5 Such dispersal can be continuous or semi-continuous to further assist and maximize the contact area of the heated exchange solvent relative to the thiophene mixture. This example of the invention may be especially useful in instances in which the exchange solvent, the mixture (or both) are available in limited quantities. For some applications, it may be desirable to add the mixture below the surface of the heated

10 solvent.

The methods of the invention are generally flexible and can be used to replace all or part of the water in a subject thiophene mixture with at least one other desired solvent. This feature of the invention further enhances the utility of many optionally

15 substituted mono- and polythiophenes and especially many of the Baytron™ formulations. By way of illustration and not limitation, the invention can be used to replace a pre-determined amount of water in a Baytron™ M or P formulation with at least one other solvent including a combination of different solvents. It is thus possible to make many new thiophene mixtures and particularly a wide variety of

20 converted (solvent exchanged) Baytron™ formulations. Such converted formulations having a pre-determined amount of water exchanged for solvent or combination of solvents can be used in a range of new applications.

As will be appreciated, the invention is compatible with a wide spectrum of

25 solvents. Typically, the exchange solvent will include one solvent. However, for some applications it will be useful to employ a combination of solvents as the exchanging medium e.g, two to six solvents, preferably about two solvents. In another embodiment, the invention methods can be adapted so that all or part of the water in a thiophene mixture is exchanged for a first solvent (or solvent combination).

30 If the resulting converted thiophene mixture includes unexchanged water, that water can be further exchanged (fully or partially) with a second solvent (or solvent combination), thereby making a further converted mixture. Further solvent exchange can be performed as needed. Choice of a particular solvent exchange procedure

according to the invention will be guided by recognized parameters including the use for which a particular converted thiophene mixture is intended.

5 More specific solvents of the invention include those that are stable to heat conditions favoring water vaporization. A more preferred solvent or solvent combination for use in the method has a boiling point of at least about 100°C at standard pressure (1 atmosphere (atm)). However in embodiments in which the water solvent can be vaporized below or above 100°C other solvents may be more desirable e.g, those having boiling points below or above 100°C at 1 atm. Exemplary
10 embodiments include practice of the method in which the vessel has an internal pressure less or greater than about 1 atm. More specific exchange solvent examples include polar and non-polar solvents as well as solvents that are miscible or insoluble in water.

15 As mentioned, the invention provides compositions made entirely or in part with at least one of the converted (solvent exchanged) thiophene mixtures according to the invention. In one embodiment, the composition is an azeotrope. That is, the composition cannot be separated by fractional distillation into two or more pure substances. Such azeotropes include maximum-boiling azeotropes in which the
20 boiling point of the heated solvent is raised by contact with the water solvent. Also included are minimum-boiling azeotropes in which the boiling point of the heated solvent is depressed by contact with the water solvent.

Preferred compositions of the invention feature an electrical conductivity that
25 is at least about an order of magnitude larger than the corresponding unconverted (no solvent exchange) thiophene mixture when measured according to standard procedures. Particular converted polydioxothiophenes of the invention such as TOR-CP exhibit a conductivity increase that is about one to two orders of magnitude greater than Baytron™ P.

30

In another embodiment, the invention features more particular methods that include forming a composition from the mixture, preferably a coating composition, and subjecting that composition to at least one drying treatment step as defined herein.

Preferably, the drying treatment is performed after step c) of the method (ie. solvent exchange step). Such treatment may be performed once or more than once as needed. More preferred drying treatments involve significant exposure to ambient room temperature or higher temperatures sufficient to remove solvent from the composition. In embodiments in which more than one drying treatment is desired eg., two, three or four of such treatments, the drying treatments may be the same or different as needed to achieve a particular result. In such embodiments, the drying treatments can be performed in a tandem or discontinuous format. Generally, but not exclusively, drying treatments of less than about one to two days are suitable for most invention applications. Less than about several hours, preferably less than a few hours will be preferred for most invention applications. Compositions produced by such methods are also featured herein.

In yet another aspect, the invention provides conductive materials, particularly coating materials and films that include or consist of the compositions provided by this invention. Preferred films suitably include at least one polymer, co-polymer or mixture thereof such as those disclosed below. Such conductive materials are well-adapted for use in anti-static or electrostatic applications.

Also featured are conductive coatings that include or consist of the compositions provided herein, preferably configured as a layer having at least one of the following performance characteristics: 1) good resistivity; 2) good surface resistance; and 3) good optical transmission. Preferably, such compositions exhibit at least good resistivity. Examples of preferred conductive coatings are provided in the discussion that follows.

Also provided by the invention are articles of manufacture that include or consist of at least one of the compositions and coating materials of this invention.

In one embodiment, the articles are electro-optical implementations and preferably organic light emitting devices (OLED) such as those provided below.

In another aspect, the invention provides useful methods for making an electronic implementation, typically by "writing" or "printing", which methods include at least one and preferably all of the following steps:

- 5 a) contacting at least one of the compositions disclosed herein with a first polymer layer,
- b) dissolving at least a portion of the first polymer layer with the composition under conditions forming a hole, typically a via-hole or interconnect, in the first polymer layer; and
- 10 c) evaporating the solvent in the composition to make the electronic implementation.

The foregoing method for making the electronic implementation has important advantages including providing better control of solvent surface tension as well as enhanced writing or printing alignment of the hole. Also provided are electronic
15 implementations and manufactured articles produced by the method.

BRIEF DESCRIPTION OF THE DRAWINGS

Figure 1 is a graph showing optical transmission versus surface resistance of a
20 converted (solvent exchanged) TOR-CP (Triton AO Resistant Conductive Polymer made from converted Baytron™ P) and Baytron P (neat). The TOR-CP was filtered or non-filtered.

Figure 2 is a graph showing volume resistance comparisons of TOR-CP
25 exchanged with N-methylpyrrolidone (NMP) in Matrimid™ (Ciba) as polyimide; TOR-CP exchanged with di-methylacetamide (DMAC) in TOR-NC (Triton AO Resistant polyimide); and TOR-CP exchanged with NMP in TOR-NC.

Figure 3 is a graph showing bulk film light transmission versus volume
30 resistance for the polymers described in Figure 2, above.

Figure 4 is a table showing data from eight (8) samples of Baytron™ P exchanged with NMP. The data provide conductivity, viscosity, solids content, particle size distribution, transmission, pH, density, and water content parameters.

5 Figure 5 is a table showing data from eight (8) samples of Baytron™ P exchanged with NMP. The data provide conductivity, viscosity, solids content, particle size distribution, transmission, pH, density, and water content parameters.

10 Figure 6 is a table showing data from ten (10) samples of Baytron™ P exchanged with NMP. Also shown are data from six (6) samples of neat (non-solvent exchanged) Baytron™ P.

15 Figures 7A, 7B, and 7C are tables showing data from selected samples of Baytron™ P exchanged with NMP or DMAc. Drawdown surface resistances are also illustrated.

Figure 8 is a formulation performance table showing thickness and resistance properties of several TOR-CP batches.

20 Figures 9A-D are graphs showing resistivities of spin-coated films of TOR-CP and Baytron-P on glass substrates as a function of coating thickness.

25 Figure 10 is a graph showing optical transparencies of spin-coated films of TOR-CP and Baytron-P on glass substrates as a function of wavelength.

Figure 11 is a graph showing performance of a OLED of the invention made with TOR-CP as a hole injection layer (HIL).

30 Figure 12 is a table showing resistivity and surface resistance data for selected TOR-CP and Baytron-P samples. The data generally show that TOR-CP features better surface resistance and resistivity characteristics than Baytron-P.

Figure 13 is a graph showing surface resistance of CP coatings and Baytron P on a PET substrate

Figure 14 is graph showing light transmittance of CP coatings and Baytron P on a PET substrate.

5 Figure 15 is a table showing data in support of Figures 13 and 14.

Figure 16 is a graph showing Ln-Ln conductivity data of Tor-CP and Baytron P at various temperatures.

10 Figure 17 is also a graph showing Ln-Ln conductivity data of Tor-CP and Baytron P at various temperatures.

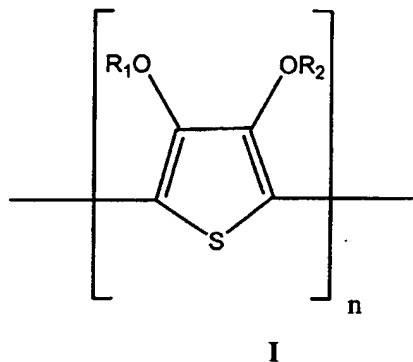
DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

15 As discussed, the invention provides highly useful methods for replacing some or all of the water associated with many thiophenes, preferably optionally substituted mono- and polythiophene mixtures. More preferred mixtures include Baytron™ formulations provided as M or P type. The invention has a variety of important applications including providing electrically conductive compositions useful in the
20 manufacture of anti-static and electrostatic coatings, capacitor electrodes (tantalum and aluminum, for example), and through-hole plating of printed circuit boards (PCBs). Further uses and advantages of the invention are discussed below.

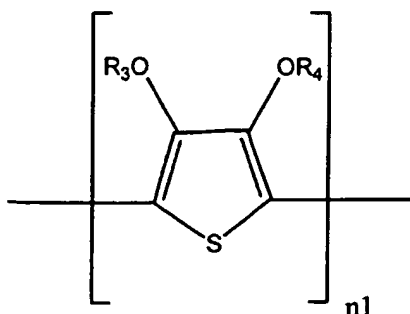
By the term "converted" "solvent exchange", "solvent exchanged" or like
25 words or phrases is meant replacement of some or all of the water associated with the thiophene mixture for a desired exchange solvent (or combination of solvents). Preferably, the replacement of the water is at least about 30% (w/v) complete, more preferably at least about 50% (w/v), even more preferably at least about 90% (w/v) complete, most preferably at least about 99% (w/v) complete with respect to the total
30 volume of water originally present in the mixture. As mentioned, it is an object of the invention to reduce the amount of water present in the thiophene mixture sufficient to replace at least some of that water and sometimes essentially all of the water with a desired volume of the exchange solvent or solvent combination. For many invention

applications, substantially complete substitution of the desired solvent or solvent combination for the water in the mixture will be generally preferred.

The invention is fully compatible with a wide range of thiophene mixtures. A thiophene mixture refers to a material that includes at least one optionally substituted mono- or polythiophenes thiophene as disclosed herein which mixture preferably includes water and optionally other components such as, but not limited to, counterions, stabilizers, ect. Preferred are cationically charged monodioxothiophenes and polydioxothiophenes represented by the following formulae I and II:



wherein R1 and R2 each independently represent hydrogen or an optionally substituted C1-C6 alkyl group, or together form an optionally substituted C1-C6 radical, preferably a methylene radical which is optionally substituted by lower alkyl groups, an ethylene-1,2 radical optionally substituted by C1-C12 lower alkyl or phenyl groups, or an optionally substituted cyclohexylene-1,2 radical, n is 1; and the polythiophene is represented by the following formula (II):



II

wherein R3 and R4 each independently represent hydrogen or an optionally substituted C1-C6 alkyl group, or together form an optionally substituted C1-C6 radical, preferably a methylene radical which is optionally substituted by lower alkyl groups, an ethylene-1,2 radical optionally substituted by C1-C12 lower alkyl or phenyl groups, or an optionally substituted cyclohexylene-1,2 radical. Preferably, n1 in Formula II is greater than 1, preferably about 2 to about 10,000, with between from about 5 to about 5000 being preferred for many applications.

10

By the term "optionally substituted" is meant substitution with hydrogen, substituted or unsubstituted (C1 -C18)-alkyl, preferably (C1 -C10)-, in particular (C1 -C6)-alkyl, (C2 -C12)-alkenyl, preferably (C2 -C8)-alkenyl, (C3 -C7)-cycloalkyl, preferably cyclopentyl or cyclohexyl, (C7 -C15)-aralkyl, preferably phenyl-(C1 -C4)-alkyl, (C6 -C10)-aryl, preferably phenyl or naphthyl, (C1 -C18)-alkyloxy, preferably (C1 -C10)-alkyloxy, for example methoxy, ethoxy, n- or iso-propoxy, or (C2 -C18)-alkyloxy ester. Exemplary substitution groups include halogen, particularly chlorine, fluorine and bromine; lower alkyl, alkenyl, alkynyl, or alkoxy having 1 to 6 carbons, hydroxy, keto, allyl, and sulphonate, for example.

20

More specific examples of the mono- and polydioxothiophenes have been reported in U.S. Pat. Nos. 5,766,515, 6,083,835, 5,300,575, 6,157,479, EP-A 440 957, EP-A 339,340; the disclosures of which are incorporated herein by reference. Particular thiophenes of interest may, but do not necessarily include, one or more organic compounds containing dihydroxy or polyhydroxy, and/or carboxyl groups or amide groups e.g., lactam groups are N-methylpyrrolidone, pyrrolidone, caprolactam, N-methylcaprolactam, N-octylpyrrolidone. In embodiments in which such organic compounds are desired, the mono- and polythiophenes will further include sugar and sugar derivatives such as sucrose, glucose, fructose, lactose; sugar alcohols such as sorbitol, mannitol; furan derivatives such as 2-furancarboxylic acid, 3-furancarboxylic acid; alcohols such as ethylene glycol, glycerol, di- or triethylene glycol. See the U.S. Pat. No. 6,083,635, for example.

30

In many invention embodiments, the cationically charged monodioxothiophenes and polydioxothiophenes of Formulae I and II above, are each associated with one or more suitable polyanions. Preferred polyanions are the anions of polymeric carboxylic acids such as polyacrylic acids, polymethacrylic acids or
5 polymaleic acids or of polymeric sulphonic acids such as polystyrenesulphonic acids and polyvinylsulphonic acids. These polycarboxylic and polysulphonic acids can also be copolymers of vinylcarboxylic and vinylsulphonic acids with other polymerizable monomers such as acrylic esters and styrene. The anion of polystyrenesulphonic acid is particularly preferred as counterion in most invention embodiments.

10

The molecular weight of the polyacids providing the polyanions is preferably from 1000 to 2,000,000, particularly preferably from 2000 to 500,000. The polyacids or their alkali metal salts are commercially available, e.g. polystyrenesulphonic acids and polyacrylic acids, or else can be prepared by known methods. Other suitable
15 polyanions include mixtures of alkali metal salts of polyacids and corresponding amounts of monoacids. See the U.S. Pat. No. 6,157,479 and references cited therein.

Additionally preferred thiophenes according to the above Formulae I and II include those in which R1, R2, R3 and R4 each independently represent C1-C4 alkyl
20 or together form a C1-C4 radical. More preferably, the monothiophene is an optionally substituted mono-3,4-alkylene dioxothiophene such as mono-3,4-ethylene dioxothiophene. Preferred polythiophenes include poly-3,4-alkylene dioxothiophene, preferably poly-3,4-ethylene dioxothiophene.

25 See also U.S. Pat. Nos. 5,294,372 and 5,066,731 for disclosure relating to other preferred thiophenes including mono- and polydioxothiophenes.

More specifically preferred mono- and polydioxothiophenes according to the invention are Baytron™ formulations (Bayer Corporation, 100 Bayer Rd. Pittsburgh,
30 PA 15205-9741). Such polymer formulations are reported to be highly useful in the manufacture of organic conductive polymers. Specific examples of such formulations include, but are not limited to, those designated as M or P formulations. Preferred P type formulations include CPUD2, CPP103T, CPP105T, CPP116.6, CPP134.18,

CP135, CPP 4531 I, CPP 4531 E3 and CPG 130.6. A preferred Baytron™ M formulation is a monomer of poly(3,4-ethylenedioxythiophene).

Although it will often be helpful to convert the Baytron™ M to its
5 corresponding polymeric form before practicing the invention, use of Baytron™ M in the methods of this invention is contemplated particularly in cases in which solvent exchanged Baytron™ M formulations are desired. Procedures for converting Baytron™ M to its polymeric form have been disclosed by the Bayer Corporation.

10 See also the following patent references for additional examples of suitable substituted or unsubstituted thiophene-containing polymers: U.S. Pat. Nos. 4,731,408; 4,959,430; 4,987,042; 5,035,926; 5,300,575; 5,312,681; 5,354,613; 5,370,981; 5,372,924; 5,391,472; 5,403,467; 5,443,944; 5,463,056; 5,575,898; and 5,747,412; the disclosures of which are each incorporated herein by reference.

15 As discussed, the invention is fully compatible with use of a wide array of solvents and solvent combinations. Generally, choice of an exchange solvent or solvent combination will be guided by recognized parameters including intended use for the converted (solvent exchanged) mono- or polythiophene. A more specific
20 example of such a solvent is one that is stable (ie. does not degrade) to at least about 100°C at standard temperature and pressure (STP). A preferred solvent boiling point is between from about 100°C to about 250°C at STP. Additionally preferred solvents can be fully or partially water soluble or water insoluble as needed. By the term "solvent combination" or like phrase is meant at least two mutually miscible solvents,
25 preferably two, three or four of such solvents.

More examples of suitable solvents include lower alkyl acetamides, lower alcohols including diols and triols, pyrrolidones, lower alkyl pyrrolidones, higher alkyl pyrrolidones, lower alkyl sulfoxides; as well as mixtures thereof. A preferred
30 lower alcohol is glycol or glycerin. Suitable lower alkyl sulfoxides include dimethylsulfoxide (DMSO). Specifically preferred solvents for many invention embodiments are di-methylacetamide (DMAC) and N-methylpyrrolidone (NMP). By the term "lower alkyl" is meant between from about 1 to 20 carbon atoms (branched

or straight chain), preferably about 1 to about 10 of such carbon atoms, more preferably about 1 to about 4 of such carbon atoms.

More particular solvents and co-solvents according to the invention will vary
5 e.g., according to intended use. Example of such co-solvents and solvents include, but are not limited to, acetonitrile, benzonitrile, lower alkyl cyanoacetates, preferably methylcyanoacetate; halogenated methanes, preferably dichloromethane; diethyl ether, lower alkoxy ethanes, preferably dimethoxyethane; N,N-dimethylformamide, nitrobenzene, nitromethane, propionitrile, and propylene carbonate. By the term
10 "lower alkoxy" is meant methoxy, ethoxy, propoxy, isopropoxy, butyoxo; preferably methoxy. A preferred halogenated methane is partially or fully chlorinated or brominated e.g., dichloromethane and dibromomethane.

One or more of the foregoing preferred solvents can be combined to provide a
15 solvent combination. An illustrative solvent combination would be a mixture of NMP and DMAc, eg., a 50:50 (v/v) mixture of those two solvents. Choice of a particular solvent combination will be guided by intended use of the converted thiophene.

As mentioned previously, the invention is flexible and can be performed by
20 use of one or a combination of strategies. Preferred practice of the invention involves obtaining a suitable solvent or solvent combination and adding that solvent to a vessel. Typically, the exchange solvent or combination is heated in the vessel to a temperature of between from about 100°C to about 250°C. In most invention embodiments, the vessel conditions further include exposing the solvent to a pressure
25 of about 1 atm, although greater or less pressures may be more suitable for other applications.

Subsequently, about 1 part of the mixture comprising the optionally substituted mono- or polythiophene to at least about 2 parts heated solvent per minute.
30 Preferably, the addition step further includes adding about 1 part of the mixture to between from about 2 to about 10,000,000 parts heated solvent per minute, preferably about 3 to about 100 parts of the heated solvent per minute. Preferred contact between the heated solvent (large volume) and the mixture (smaller volume) moves heat quickly into the mixture sufficient to make the water vapor. In this example of

the invention, the larger solvent volume (relative to the mixture volume) facilitates heat transfer to the mixture and production of water vapor.

5 In a preferred embodiment, it is helpful to collect the water vapor from the mixture as a condensate or distillate separated from the vessel. Preferably, a chamber or trap is used to catch and retain the condensed water vapor. The trap can be configured with a cooling apparatus such as a cooling condenser to assist condensation of the water vapor if desired. In embodiments in which the trap is used, it is possible to measure the amount of water collected, thereby allowing quantitation
10 of the water vapor captured from the mixture entering the vessel. This feature of the invention provides many advantages eg., it allows the invention user to monitor the amount of water removed from the system as the solvent exchange process occurs. Moreover, the user can control the duration and extent of water solvent removal eg., by adjusting the heat of the exchange solvent and/or flow of the mixture into the
15 reaction vessel. Thus, the user can readily quantify solvent replacement by simple inspection of the water collected in the trap. The precise amount of water removed from the mixture as vapor will vary depending e.g., on the intended use for the converted mixture. Preferably, less than about 100% (w/v) of the water is removed from the mixture as vapor, more preferably, between from about 1% (w/v) to about
20 95% (w/v) of the water is removed.

Specific adaptations of the foregoing methods can facilitate the solvent exchange process.

25 For example, it will often be very helpful to provide conditions of high sheer mixing between the thiophene mixture and the exchanging solvent. Preferred conditions reduce or prevent agglomeration (congealing) of the Baytron™ P beyond a particle size of about 1 micron. Many Baytron™ P formulations are provided as dispersions in which each particle has a size of about 1 micron. In embodiments in
30 which the high sheer mixing conditions are employed, presence of unsuitably large particles and agglomerates can be reduced or avoided. The converted Baytron™ P formulations can have much better uniformity. A wide variety of mixing

implementations can be used to provide such high sheer mixing conditions. Specific examples of such implementations are provided below.

In more specific example of this invention embodiment, the method further
5 includes contacting the heated solvent with at least one non-reactive gas. That gas is typically added to the vessel as a flow or jet stream to facilitate removal of the water solvent from the mixture. Preferably, the gas flow is configured to assist movement of vaporized water toward a chamber or trap as described below. Examples of
10 suitable gases include nitrogen, a noble gas (He, Ar, ect.); or a mixture thereof. If desired, the gas can be pre-heated to about the temperature of the heated solvent to minimize cooling of the solvent in the vessel. The gas can be added to the vessel in several ways including use of a gas pump. The volume of gas introduced into the vessel will vary with intended use but will generally be sufficient to provide for good removal of water vapor from the vessel into the chamber or trap.

15
After a desired amount of the water is replaced by the exchange solvent or solvent combination, the converted thiophene mixture is collected from the vessel generally as a dispersion. In a particular example of the invention, the dispersion will essentially consist of NMP and Baytron™ P; or DMAc and Baytron™ P, or ethylene
20 glycol and Baytron™ P. Such dispersions according to the invention are well-suited for the uses disclosed herein including those specific applications intended for Baytron™ formulations. If needed, the solvent exchange methods of this invention can be repeated e.g., one, two or three times, with the already converted thiophene mixture to introduce one or more other desired solvents therein including
25 combinations of the same or different solvents.

A more specific solvent exchange method according to the invention involves exchanging di-methylacetamide (DMAc) or N-methylpyrrolidone (NMP) or ethylene glycol for water in a colloidal water dispersion that includes at least one poly-3,4-
30 ethylene dioxythiophene preparation. An example of a preferred preparation is Baytron™, preferably Baytron™ P. In one invention embodiment, the method includes at least one and preferably all of the following steps:

- a) heating an amount di-methylacetamide (DMAC) or N-methylpyrrolidone (NMP) or ethylene glycol in a first vessel to a temperature of between from about 100°C to about 250°C,
- b) contacting the heated di-methylacetamide (DMAC) or N-methylpyrrolidone (NMP) or ethylene glycol with an amount of the colloidal water dispersion comprising water and poly-3,4-ethylene dioxythiophene, wherein the dispersion is added to the surface of the heated solvent at a rate of between from about 0.1 to about 1000 mls/minute, preferably about 1 to 100 mls/minute, more preferably about 10 mls/minute, the contact being sufficient to remove at least part of the water from the dispersion as vapor; and
- c) exchanging the water removed from the dispersion as vapor with the di-methylacetamide (DMAC) or N-methylpyrrolidone (NMP) or ethylene glycol.

In one embodiment of the foregoing method, that method further includes removing at least part of the water from the vessel as vapor. If desired, that water vapor can be collected or condensed into a second vessel (ie. chamber or trap) that includes at least one co-solvent. The co-solvent can be the same or different from the exchange solvent used in the vessel. In this invention example, the method further includes condensing the water vapor into a second vessel comprising at least one co-solvent.

As mentioned, it is usually desirable to maximize contact between the exchange solvent (or solvent combination) and the mixture comprising the poly-3,4-ethylene dioxythiophene preparation. For example, the ratio of the amount of the di-methylacetamide (DMAC) or N-methylpyrrolidone (NMP) or ethylene glycol solvent to the amount of the mixture is desirably more than one, preferably between from about 1.5 to about 10,000,000 or more, more preferably between from about 2 to about 10.

In a preferred example of the method, the optionally substituted poly-3,4-alkylene dioxythiophene is obtained as a colloidal water dispersion, preferably also including at least one counter ion. More preferably, the counter ion is polystyrene sulfonic acid and the optionally substituted poly-3,4-alkylene dioxythiophene is poly-

3,4-ethylene dioxothiophene. A particular example of such as polydioxothiophene is Baytron™ P.

Particular methods according to the invention involve forming a composition
5 from the mixture, preferably a conductive coating composition therefrom, and
subjecting that composition to at least one drying step, preferably after step c) (solvent
exchange step) of the methods discussed above. Typically, formation of the
composition involves isolating that material from the vessel used to conduct the
method, for instance, by filtration, centrifugation and the like.

10

The invention is compatible with a wide spectrum of drying treatment steps so
long as they facilitate production of compositions with at least good resistivity. By
the phrase "good resistivity" is meant a resistivity of between from about 0.01 to
about 1 (ohm-cm), eg., about 0.02 to about 0.6 (ohm-cm), for compositions having a
15 thickness of between from about 10nm to about 250nm, preferably about 40nm to
about 150nm. Additionally preferred drying treatment steps provide a good surface
resistance ie., between from about 100 to about 10, 000 (ohm/sq), preferably about
200 to about 650 (ohm/sq) for compositions having a thickness of between from about
10nm to about 250nm, preferably about 40nm to about 150nm. Still further preferred
20 drying treatments provide compositions with good optical transmission properties,
that is, at least about 70%, preferably at least about 90% between about 300nm and
600nm when compared with a suitable control, eg., Baytron-P.

More particular conductive coatings of the invention include at least one of the
25 compositions disclosed herein, typically one, two or three of such compositions,
preferably one of same having at least one of the following characteristics. 1) a
resistivity of between from about 0.01 to 1 (ohm cm); 2) a surface resistance of
between from about 100 to about 10,000 (ohm/sq); 3) a thickness of between about
10nm to about 250 nm; and 4) an optical transmission of at least about 90% between
30 about 300nm and 600nm wavelengths. More preferred compositions exhibit at least
two of such features, even more preferably all three of same.

It will be apparent that it is possible to relate resistivity and surface resistance,
particularly for those compositions disclosed herein provided as coating compositions.

In general, the relationship between resistivity and surface resistance is defined by the following mathematical formula:

$$\text{Resistivity} = \frac{\pi e}{\ln 2} * k * t * (V/I),$$

5

wherein, V (measured voltage)/ I (applied current) is the surface resistance with the unit of ohm/square for the four point probe measurement technique, $\pi e / (\ln 2)$ is a constant, k is the geometrical correction factor (related to film thickness, probe spacing and sample size) and t is the film thickness.

10

As discussed, the invention is compatible with a wide variety of suitable drying treatments.

For example, and in one embodiment, the drying treatment includes subjecting a composition of the invention, preferably a coating composition, to a temperature of from between about room temperature (25°C) to about 200 °C for less than about a day (24 hours). As mentioned previously, methods of the invention can include, if needed, at least two drying treatment steps the same or different. More specific drying treatments include subjecting the composition to from between about 50°C to about 150°C for less than about 12 hours, preferably about 80°C for less than about 5 hours, typically about an hour or less eg., from about 1 to about 15 minutes.

In a more specific embodiment, the drying treatment includes subjecting the coating composition to room temperature (25°C) for less about two hours or less followed by treatment at about 80°C for between from about 1 to about 15 minutes.

Preferably, the composition has a thickness of from between about 50nm to about 1000nm, preferably from between about 60nm to about 750nm.

As also discussed, the invention also provides compositions made in accord with the solvent exchange methods disclosed herein. An example of such a composition is an optionally substituted mono-3,4-alkylene dioxythiophene or poly-3,4-alkylene dioxythiophene. Preferably, that composition has between from about 1% (w/v) to about 100% (w/v) di-methylacetamide (DMAC) or N-methylpyrrolidone (NMP) or ethylene glycol. Preferably, the he optionally substituted mono-3,4-

alkylene dioxythiophene is mono-3,4-ethylene dioxythiophene commercially available as Baytron™ M. Also preferably, the optionally substituted poly-3,4-alkylene dioxythiophene is poly-3,4-ethylene dioxythiophene commercially available as or Baytron™ P.

5

Preferred compositions according to the invention can also include at least one additive such as those particular additive disclosed previously. An example of such an additive is ferric toluene sulfonic acid (Baytron™ C). Preferably, the ferric toluene sulfonic acid is present in the composition in trace amounts.

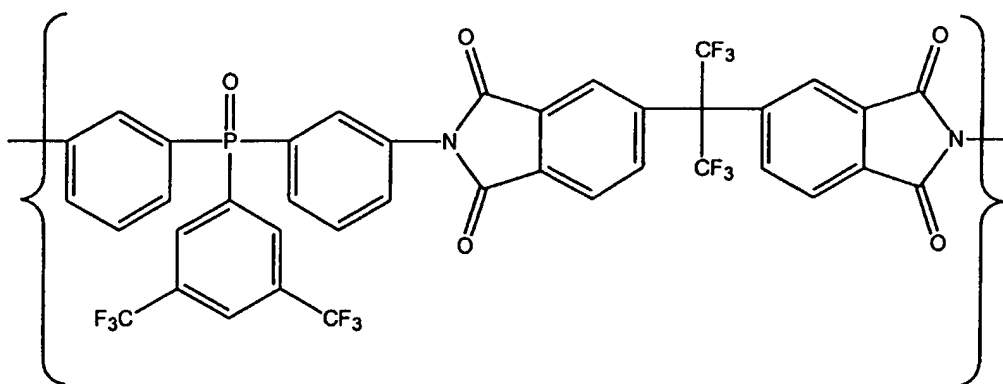
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In some embodiments, it will be desirable to combine the compositions of this invention with at least one additive. Suitable organic, polymeric binders and/or organic, low-molecular cross-linking agents may also be added to the coating solutions according to the invention. Appropriate binders are described, for example, in EP-A 564 911. Epoxysilanes, such as those provided by the EP-A 564 911 application, can be added to the coating solutions according to the invention, particularly for the production of adhesive layers on glass.

Particular converted polydioxythiophene compositions are preferably used in what is known in the field as a dispersion or solution in a cationic form. That is, a form in which those compositions are obtained, for example, by treating the thiophenes with oxidizing agents. Known oxidizing agents, such as potassium peroxodisulphate are typically used for the oxidation. Also typically, oxidized mono- and polydioxythiophenes acquire positive charges. These charges are not shown in Formulae I and II above, since the number and positions of such charges are not needed to understand and appreciate the invention.

More specific polydioxythiophene compositions according to the invention contain, based on the sum of polythiophene cations and polyanions, that is, based on the total solids content of the solution, from 1 to 100,000% by weight, preferably 10 to 1,000% by weight, of the compounds of Formulae I and II including hydroxy and carboxyl groups. More preferred compositions of this invention are water soluble.

As also discussed, the invention features a wide spectrum of compositions particularly in coating or film formats. Preferred coating compositions include at least one of the foregoing converted (solvent exchanged) optionally substituted polythiophenes, and at least one suitable organic polymer, co-polymer or mixture thereof. Methods for adding such polymers to the converted polythiophenes are known in the field and are exemplified below. Suitable polymers, co-polymers and mixtures include, but are not limited to, polycarbonate, polystyrene, polyacrylates, polyesters such as polyethylene terephthalate, polybutylene terephthalate, polyethylene naphthalate, polyamides, polyimides, optionally glass-fibre reinforced epoxy resins, cellulose derivatives such as cellulose triacetate, polyolefins such as polyethylene, polypropylene. Examples of preferred polyimides for use in preparing the films include TOR-NC (Triton Systems, Inc.), Matrimid (1,3-isobenzofulrandione, 5,5'-carbonylbis-polymer with 1 (or 3)-(4-aminophenyl)-2,3 dihydro-1,3,3 (or 1,1,3)-trim 5-amine) (Ciba); and Aurum (Mitsui Toatsu). The TOR-NC has a chemical structure represented by the following Formula III:



III

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More preferred coatings and films of the invention are conductive and include a weight ratio of at least one of the converted thiophene to the foregoing polymers, co-polymers, graft co-polymers (eg., TOR-NC, Matrimid, Aurum, or a mixture thereof) is about 10:90 to about 0.1 to 99.9, preferably 6:94 to about 0.5:99.5. A preferred film composition is the TOR-NC polyimide and converted Baytron™ P

formulation (TOR-CP, see below). Other polyimides and/or polydioxothiophene combinations may be better suited for other applications.

5 In invention embodiments in which the Baytron™ P polydioxothiophene (or polythiophene made from Baytron™ M) has at least about 90% (w/v) of the water solvent exchanged with NMP or DMAc or ethylene glycol, preferably at least about 95% (w/v) of the water solvent exchanged with NMP or DMAc, and more preferably at least about 99% (w/v) up to 100% (w/v) so exchanged, the converted Baytron™ formulation will often be referred to herein as TOR-CP.

10

More preferred coating films made from TOR-CP include between from about 0.5% (w/w) to about 5% (w/w) of the TOR-CP relative to the polyimide of interest, preferably between from about 1% (w/w) to about 4% (w/w). See the Examples below as well as the Drawings.

15

Preferred coating materials of the invention include from about 1 mg/m² to about 500 mg/m² of at least one of the compositions of this invention including TOR-CP exchanged with NMP or DMAc or ethylene glycol. The TOR-CP can include one or more polyimides of interest including at least one of Matrimid and TOR-NC. Of course, other compositions as disclosed herein may be more suitable for other applications. Additionally preferred coating materials have an optical density of between from about 0.0001 to about 0.05 at between from about 300nm to about 700nm. Also preferred are those coating materials that exhibit light transmission of between from about 10% to about 95% or more, preferably 80% to about 99% or more as measured by a BYK Gardner Haze-gard plus machine. Such coating compositions will often further include at least one additive as described previously. Coating compositions having a light transmission greater than about 80% will often be preferred in many optical applications.

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The compositions of this invention including preferred conductive films and coatings can be produced by reference to recognized processes disclosed in U.S. Pat. Nos. 5,766,515, 6,083,835, 5,300,575, and 6,157,479. Preferred production processes involve, for example, spraying, application by a doctor blade, dipping, application

with roller applicator systems, by printing processes such as gravure printing, silk screen printing, curtain casting, and can be dried at room temperature or at temperatures of up to 300°C, preferably up to 200°C. Suitable substrates are transparent substrates such as glass or plastic films (e.g. polyesters, such as polyethylene terephthalate or polyethylene naphthalate, polycarbonate, polyacrylate, polysulphone or polyimide film).

The invention has other applications as well. For example, the compositions, films and coatings disclosed herein can be used to coat some or all of an organic or inorganic fiber or related substrate. Illustrative of such fibers include those made whole or in part from Kevlar™ (aramide), polyethylene, PBO (poly-benzoxazole), polyester, nylon, polyamide, glass; as well as combinations thereof. Preferred fibers are about 0.5 to 50 deniers, preferably about 1 to about 10 deniers. Application of the invention compositions, films and coatings will help improve the electrical conductivity of the fibers.

The invention is also compatible with techniques for making spin-coated filaments, particularly monofilaments, by electrospinning. See Reneker, D.H. *Nanometer Diameter Fibres of Polymer Produced by Electrospinning*, Fourth Foresight Conference on Molecular Nanotechnology .

For some applications, it will be useful to anneal the films and coatings e.g. to increase electrical conductivity. Methods for annealing a wide variety of suitable films and coatings have been disclosed in the U.S. Pat. No. 6,083,635, for example.

The coatings and films of this invention can be used in a variety of thicknesses depending, eg., on intended use and desired transparency and conductivity parameters. A preferred thickness is from about 0.005 to about 500 µm, preferably from about 0.05 to about 10 µm. Preferred conductive coating materials of this invention can be configured as a layer having a surface resistance of between from about 10 to about 10^{12} Ω/sq. Additionally preferred are coatings featuring a surface resistance of from about 10 to about 4000 Ω/sq, preferably from about 10 to about 2000 Ω/sq, more preferably from about 10 to about 1000 Ω/sq.

As disclosed herein and in the prior provisional application 06/269,606 filed on February 16, 2001, a wide spectrum of organic solvent-based conducting polymer systems, particularly TOR-CP[™] has been provided. Tor-CP is PEDOT:PSS based
5 organic solvent systems, such as NMP, which has a very low water content of less than 3% water. The present invention is further investigation of the Tor-CP-based coatings for the electro-optic device applications. Electrical resistivity measurement results indicated that coatings produced using Tor-CP exhibited higher electrical conductivity than that of the state-of-the-art conducting polymer systems such as
10 PEDOT:PSS supplied by Bayer AG (trade name Baytron-P). Furthermore, optical transparencies of the coatings using Tor-CP are similar to that of the Baytron-P. In addition, resulting coating are very stable in the ambient laboratory atmosphere. Applicants have not observed any degradation of coating properties during exposure to unprotected ambient atmosphere longer than one month. During the same period,
15 coatings prepared using the Baytron-P and stored in the same environment degrades (seriously softened), probably due to reaction with moisture.

Excellent electric conductivity, high optical transparency and environmental stability of the coatings from Tor-CP suggest that Tor-CP is an ideal candidate
20 material for many electro-optic device applications. Furthermore, low water contents in the Tor-CP will provide additional benefit of ease-of manufacturing of electro-optic devices that contain ITO electrodes. In addition, the non-acidic and non-hygroscopic nature of the coatings from Tor-CP further suggest a long lifetime or less performance degradation of the devices fabricated using Tor-CP. The unique properties of the
25 coatings from Tor-CP further suggest that present transparent electrodes of ITO can be replaced by coating from Tor-CP for a certain applications. In such case, all organic material based electro-optic devices can be realized, including flexible plastic (or polymer) substrates that will significantly reduce manufacturing costs of many electro-optic devices and provide opportunities of producing advanced electro-optic
30 devices that requires flexible substrates.

Furthermore, the electric conductivity of the Tor-CP coatings can be significantly increased without degrading the optical transparency by employing specially designed coating fabrication processes.

The conductive films and coatings according to the invention find use in a wide range of applications requiring good electrical conductivity e.g., as electrodes in electroluminescent displays, in LCD displays, in solid electrolyte capacitors, for the deposition of metals such as copper, nickel, for example, in the manufacture of printed circuits, in solar cells, in electrochromic displays or for the screening of electromagnetic radiation or for leading away electrical charges, for example, in picture tubes or as anticorrosive coatings on metals, for the production of touch screens. Other areas of application are systems for picture production, for example, silver halide photography, dry-plate systems, electrophotography.

The conductive coatings and films of the invention are well-suited for optional coating with further layers such as those reported in the U.S. Pat. No. 6,083,635, for example.

15

Also provided by the present invention are articles of manufacture that include or consist of at least one of the compositions disclosed herein. Examples of such articles include, but are not limited to, an antiradiation coating, antistatic coating, battery, catalyst, deicer panel, electrochromic window, electrochromic display, electromagnetic shielding, electromechanical actuator, electronic membrane, embedded array antenna, fuel cell, infrared reflector, intelligent material, junction device (PV), such as photovoltaic cells, lithographic resist, non-corrosive paint, non-linear optical device, conductive paint, polymer electrolyte, radar dish, redox capacitor, sealant, semiconductor circuit, sensor, smart window, telecom device, waveguide, or wire (low current). Preferably, the electromechanical actuator is one of a biomedical device, micropositioner, microsorter, microtweezer, or microvalve. Also preferably, the sensor is one of a biological, chemical, electrochemical, irradiation dosage, mechanical shock, temperature, temperature limit, or time-temperature sensor.

30

As discussed, many electro-optic devices, such as light emitting diodes (LED's) and photovoltaic cells, require electrically conductive and optically transparent films/coatings as electrode materials. Presently, transparent electrodes in electro-optic devices are made of ITO coated glass substrates. ITO has, however,

several crucial shortcomings. Its manufacturing processes involve a relatively cumbersome and costly technology, such as vacuum deposition in a controlled gas atmosphere. Furthermore, due to brittle-nature of the ITO films, it is difficult to prepare the ITO films on large area substrates or flexible substrates.

5

Currently, transparent conducting polymers and their coatings are considered the best candidate material as a hole injection layer in organic light emitting diodes (OLED's). In this application, a thin layer (less than 20nm thickness) of transparent conducting polymers is deposited by employing a solution film casting process, such as a spin-coating method, onto the ITO coated substrate. As previously mentioned, the ITO layer is deposited onto the rigid substrate, such as glass, via a vacuum deposition process. Since the ITO is very sensitive to moisture and other acid based chemicals, fabricating a hole injection layer on top of ITO requires cumbersome processes and seriously limits the selection of substrate materials.

15

Although electrically conductive and optically transparent coatings have been successfully produced using polyaniline (PANI) containing solution (U.S. Patent No. 5618469) and PEDOT/PSS polymer dispersion (Eur Patent 686662), these prior art inventions have serious limitations in manufacturing practical electro-optic devices. For example, it is well known that the PANI systems are not stable and, therefore, it's device performance degrades rapidly over time. Performances of the carefully fabricated PEDOT:PSS-based devices are known to be stable in use. However, currently available PEDOT/PSS polymers are an aqueous based system. Therefore, fabricating PEDOT:PSS coatings onto ITO coated substrates requires cumbersome manufacturing processes. Further hydrophilic nature of the PEDOT:PSS system attracts moisture, even through the protective moisture barrier, and can induce premature failure of the devices during use.

As mentioned previously, additional articles of manufacture in accord with the invention include or consist of at least one electro-optical implementation eg., one, two, three or more of same. Preferred implementations include organic light emitting devices (OLEDs), electro-optical switches, photovoltaic cells and the like.

In preferred embodiments, the OLED includes at least one and typically all of the following components operatively linked together: 1) metal cathode; 2) electron transport layer (ETL); 3) organic emitter; 4) hole injection layer (HIL); and 5) a glass substrate layer. Optionally, the OLED further includes an indium doped tin oxide (ITO) anode operatively linked to the same. A representation of such an OLED structure has been reported by Cropper, A.D. et al. in *Organic Light-Emitting Materials and Devices IV*, Kafafi, Z. H. Editor, Proceedings of SPIE, Vol. 4105 18-29 (2001). See Figure 2 of Cropper, A.D. et al. entitled "OLED basic structure" in particular. By the phrase "operatively linked together" is meant association of such components in a configuration necessary to achieve suitable functionality of the OLED.

It is an object of this invention to replace the ITO of the OLED with at least one of the compositions disclosed herein, preferably one of the conducting compositions. This feature of the invention provides advantages including better performance characteristics, especially improved conductivity and optical transparency. Preferred OLEDs of the invention will include at least one of the compositions disclosed herein provided as the hole injection layer (HIL). An especially preferred OLED includes TOR-CP as the HIL.

20

In a more particular example of the invention, the OLED has a peak external quantum efficiency of between about 0.02% to about 0.2%, preferably when such OLED is operated between from about 4 to about 8 volts.

25

Additionally preferred OLEDs of the invention have a peak power efficiency of between from about 0.5 to about 2 lm/W at an applied bias of between from about 1 to about 8 volts.

30

Still further preferred OLEDs have a luminance of between about 7000 to about 9000 cd/m². Preferably, the OLED has a maximal luminance of between from about 10,000 to about 50,000 cd/m² at about 4 to about 8 volts.

As mentioned the invention also provides suitable methods for making an electronic implementation by writing or printing manipulations. Preferably, such

methods are performed repetitively or semi-repetitively e.g., as when at least step a) is repeated at least once. In a particular method steps a), b) and c) are repeated twice or more to print or write the electronic implementation.

5 In other preferred embodiments of the method, the hole (via-hole or interconnect) produced by dissolution of the first polymer layer by the exchange solvent in the composition includes a first end contacting the first polymer layer and a second end contacting a substrate layer. That hole is substantially filled with the composition according to the method, preferably with the assistance of a conventional
10 ink-jet printer. One suitable ink-jet printer includes at least two nozzles for dispersing the composition of the invention, each nozzle comprising the same or different composition as needed. Preferably, at least one of the compositions comprises poly(3,4-ethylenedioxy-thiophene) which composition may further include polystyrene sulfonic acid (PEDOT/PSS). A more preferred composition for use with
15 the method for making the electronic implementation is Baytron™-P or a suitable polymer of Baytron™-M.

In one embodiment of the method for making the electronic implementation, the first polymer layer comprises or consists of a dielectric polymer e.g.,
20 polyvinylphenol, polyimide and polycarbonate. Preferably, the substrate layer is insoluble in the solvent of the composition. An exemplary substrate is glass.

In another invention example, the electronic implementation produced by the method is an inverter capable of converting a high-voltage input to a low-voltage
25 output; or a low-voltage input to a high-voltage output. Methods for making and using inverters have been described. A more preferred inverter is a component of an electronic circuit which circuit comprises at least one source electrode and at least one drain electrode. Typically, such electrodes are separated from each other by about 1 to 10 micrometers. See e.g., Dagni, R. in *Chemistry and Engineering*, January 1,
30 2001, pp. 26-27 as well as references cited therein.

The invention methods can also be used to make useful electronic circuits having a preferred output of between from about -20V to about 0V. Additionally

useful electronic circuits have as an input between from about 0V to about -20V. Methods for making and using electronic circuits have been described. See e.g., the website at plasticlogic.com as well as references cited therein, the disclosure of which is incorporated herein by reference.

5

As mentioned, the invention also provides articles of manufacture that include the electronic implementations of this invention. Exemplary articles include a liquid crystal display, electrophoretic ink display, polymer disperse liquid crystal (PDLC) or an identification tag such as a smart label adapted for use in consumer good.

10 Particular examples of such consumer goods include s a toy or supermarket item.

In particular invention embodiments, electrically conductive and optically transparent organic solvent based polymer coatings are provided. Also provided are methods for the preparation of the same for applications of which flexibility and
15 environmental stability are of an important consideration.

In addition, the present invention also relates to a method for preparing coatings of organic solvent based poly(ethylenedioxythiophene):poly(styrene sulfonic acid) (PEDT:PSS) conducting polymers for improved properties, such as electrical
20 conductivity, of the resulting coatings for use in electro-optic devices comprising transparent electrodes which are made of same. In this embodiment the organic solvent-based polymeric system does not have compatibility problems with the state-of-the-art transparent conductive layer of indium doped tin oxides (ITO). Therefore, manufacturing processes of electro-optic devices can be easier. Furthermore, high
25 conductivity and optical transparency of the resulting films from the organic solvent based conducting polymer system suggest a possibility of replacing the ITO layer in many electro-optic device applications such as organic light emitting diodes (OLED's), photovoltaic cells, electro-optic switches, etc.

30 As shown in the Example 8, below, a thin layer (less than 20nm thickness) of transparent conducting polymers is deposited by employing a solution film casting process, such as a spin-coating method, onto the ITO coated substrate. As previously mentioned, the ITO layer is deposited onto the rigid substrate, such as glass, via a vacuum deposition process. Since the ITO is very sensitive to moisture and other acid

based chemicals, fabricating a hole injection layer on top of ITO requires cumbersome processes and serious limits the selection of substrate materials.

Additionally preferred conductive coatings in accord with the invention
5 feature a surface resistance of between about 10 ohm/sq to about 1000 ohm/sq when spin-coated in less than about 10 layers, preferably less than about 5 of same, more preferably about 1, 2 or 3 of such layers. Preferred spin-coated layers are less than about 1000 nm thick, more preferably about 100 nm thick although thinner layers may be more appropriate for some invention applications.

10

Further preferred conductive coatings have a light transmittance of at least about 80%, preferably greater than about 85%, more between from about 86% to about 95% as determined by conventional procedures disclosed herein. Additionally preferred conductive coatings exhibit such favorable light transmission properties
15 when spin-coated in less than about 10 layers, preferably less than about 5 of same, more preferably about 1, 2 or 3 of such layers. Preferred spin-coated layers are less than about 1000 nm thick, more preferably about 100nm thick although thinner layers may be more appropriate for some invention applications. Such preferred conductive coatings have a wide variety of applications including use as an anode electrode. See
20 Example 9 and Figures 14-15, for instance.

In embodiments in which the anode electrode includes (or consists of) one or more of the conductive coatings disclosed herein, such an electrode will feature a surface resistance of less than about 5 kohm/sq, preferably less than about one
25 kohm/sq to about two kohm/sq. Additionally preferred electrodes have an optical transmission of at least about 85%.

Additionally preferred conductive coatings in accord with the invention exhibit favorable resistivity and conductivity when featured on an Ln-Ln conductivity
30 graph. See Example 10 and Figures 16 and 17. Particular coatings exhibit at least about 1 Ln-sigma (S/cm), preferably between from about 1 Ln-sigma (S/cm) to about 10 Ln-sigma (S/cm), more preferably between from about 1 Ln-sigma (S/cm) to about 4 Ln-sigma (S/cm). Further preferred conductive coatings feature such good

conductivity at high temperatures of between from about 0.01 Ln-Temp ($K^{-1/2}$) to about 0.2 Ln-Temp ($K^{-1/2}$).

Still further preferred conductive coatings do not exhibit what is known as a "kink", particularly between about 0.05 Ln-Temp ($K^{-1/2}$) to about 0.1 Ln-Temp ($K^{-1/2}$), preferably between from about 0.06 Ln-Temp ($K^{-1/2}$) to about 0.08 Ln-Temp ($K^{-1/2}$). See Example 10 and Figure 17.

Additionally preferred conductive coatings of the invention exhibit good conductivity ie., at least about 1 Ln-sigma (S/cm), between from about 0.1 Ln-Temp ($K^{-1/4}$) to about 0.5 Ln-Temp ($K^{-1/4}$), preferably from about 0.2 Ln-Temp ($K^{-1/4}$) to about 0.35 Ln-Temp ($K^{-1/4}$). Also preferred are conductive coatings that do not exhibit the "kink" between about 0.2 Ln-Temp ($K^{-1/4}$) to about 0.4 Ln-Temp ($K^{-1/4}$), preferably between from about 0.24 Ln-Temp ($K^{-1/4}$) to about 0.3 Ln-Temp ($K^{-1/4}$). See Example 10 and Figure 17.

The following examples are provided to point out preferred aspects of the invention and are not intended to be indicative of the scope of the invention.

Example 1- Solvent Exchange Process for making TOR-CP/NMP

The following are preferred processes for making TOR-CP using N-methylpyrrolidone (NMP) as the exchange solvent.

A. Method 1

1. Place the Ace Glass 22L RB 4 neck flask into the Glas-Col heating mantle canister
2. Take the Ace Glass 19mm stir shaft w/teflon paddle assembly and place into the center neck of the 22L RB flask, followed by the teflon lined stirrer bearing
3. Attach the stirrer shaft to the chuck of the Arrow 850 stirrer motor
4. Hookup the SGA variac controllers to the Glas-Col heating mantle canister

5. Attach the Dean Stark Trap to the left neck of the 22L flask, then place the Ace Glass 300mm coil condenser on top of it. A tube will then run from the top of the condenser to the nitrogen bubbler.
6. In the right neck of the 22L flask, place the teflon coated temperature probe and the nitrogen line supplied by the Gilmont instruments flowmeter.
7. Into the front neck of the 22L RB flask, charge with 10,504ml of NMP (water miscible solvent as described above)
8. Turn on the SGA variacs and heat the solvent to 135 C under agitation from the Arrow 850 stirrer motor. The stirrer setting (rpm) should not need to be changed throughout the remainder of the process
9. Set the Gilmont Instruments nitrogen flowmeter to produce a steady flow of nitrogen through the flask until it comes out the bubbler
10. Using the Watson-Marlow peristaltic pump, begin pumping 3000ml of Baytron P into the 22L RB flask at a flow rate of 10ml/minute
11. Continue pumping the Baytron P into the reactor vessel until complete (approx. 3hrs)
12. As the Baytron P is being fed into the reactor, water should start condensing and collecting in the Dean Stark trap
13. At this point, adjust the nitrogen flow meter to increase the nitrogen flow considerably, forcing the water vapor up into the coil condenser
14. The water will start to rapidly condense and collect in the Dean Stark trap. Drain the trap as needed.
15. Continue this process until the desired amount of water has been removed.
16. Shut of the variacs, continue the agitation and the nitrogen flow until the product in the flask has cooled to RT
17. Remove from product from the flask

B. Method 2

- As discussed, it will often be helpful to provide conditions of high sheer mixing between the thiophene mixture and the exchanging solvent. Such conditions can facilitate a reduction in particle agglomeration and provide for better product uniformity. High sheer mixing can be readily practiced by replacing the 4 neck flask in Method 1 (step 1) with a five neck flask. Between steps 7 and 8, for example, the reagents can be subjected to high sheer mixing by using a standard homogenizer or

disperser. A preferred homogenizer is a Model #T 25 Ultra-Turrax Disperser/Homogenizer (IKA-Works). Optimal use of the homogenizer will keep Baytron P particles from agglomerating as determined eg., by inspection.

5 **Example 2- TOR/CP Conductive Coatings**

Three types of conductive coatings have been made using the solvent exchange process of this invention.

A. TOR-CP Spin-coating

10 A conductive coating was made from the solvent exchanged TOR-CP/NMP (neat) composition prepared as described above in Example 1. Specifically, the composition was spin-coated onto a glass substrate using conventional procedures. Conductivities were measured with a Keithly 2000 4 point probe.

15 Figure 1 shows light transmission and surface resistance data when TOR-CP (unfiltered), TOR-CP (filtered), and Baytron-P converted products were tested. As can be seen from Figure 1, coatings made from the TOR-CP have better light transmission and lower surface resistance than the Baytron-P coating. Figure 1 was prepared from measurements made of TOR-CP (neat) dispersion cast onto glass.

20 Although this technique is suitable for some applications, it will often be useful to combine the TOR-CP with other components and particularly at least one polymer, co-polymer, polymer blend, ect. In many instances, the resulting film or coating will have better performance characteristics when compared to TOR-CP alone.

25 **B. TOR-CP Draw down Coatings**

Standard draw down techniques were used to apply the TOR-CP to a glass substrate. Such techniques have been described e.g, by Erichsen. Specifically, the Erichsen Testing Equipment product brochure describes such techniques.

30 This composition was coated onto glass substrates using an Erichsen Model 360 film application. Wet film thickness of 120 microns was applied and the dry film thickness for the TOR-CP samples was between 0.3 to 0.5 microns. See Figure 6.

Additional drawdown coatings using the Baytron™ P product were made in order to compare the surface resistance to each other. The surface resistance measurement was made by applying silver electrodes to the coating using IEC standard 93 (VDE 03003) and measuring resistance with an ohmmeter. The resulting
5 resistance was expressed as ohms/sq. See Figure 6.

It is significant that the surface resistance of the TOR-CP coatings was up to two orders of magnitude less resistive (ie. more conductive) than similar Baytron™ P coatings. This indicates that the conversion (solvent exchange) process boosts the
10 conductivity of the base conductive polymer in an unexpected way and significantly improves the performance of the resulting TOR-CP material.

See also Figures 7A, 7B, and 7C (showing data from selected samples of Baytron™ P exchanged with NMP or DMAc). Drawdown surface resistances are also
15 illustrated.

C. Formulated TOR-CP Coatings

Formulated TOR-CP coatings according to the invention can be applied using spin-coating or draw down procedures.
20

One method for making a formulated conductive coating is as follows. Referring to Table 1, below, listed components were combined (wt% ratios) and mixed in the order given. Mixing under constant agitation was preferred.

25

TABLE 1

Component	Manufacturer	% by Weight
TOR-CP	Triton Systems	45
Silquest A 187	Witco Surfactants GmbH	0.86
Isopropanol		53.84
Bayowet FT 229	Bayer Corp	0.30
Total		100

A coating made by this method can be applied to substrates using standard spin coating or draw down coating techniques. See sections A and B, above. The
30 coating was prepared in a glass vessel with paddle stir mechanism.

Figure 8 shows surface thickness and resistance for several TOR-CP formulated drawdown coatings. The results show favorable conductivity using this coating method.

5 **Example 3- Conductive TOR-CP Films with Polyimide**

Conductive polyimide films have been manufactured by adding dry polyimide powder to TOR-CP converted (ie. solvent exchanged) solution. See Example 1, above. Typically, the polyimide powder and TOR-CP converted materials are mixed.
10 A preferred weight ratio between the polyimide polymer and conductive polymer ranges from 94:6 to 99.5:0.5.

A more specific method for making the film is as follows. A starting quantity of TOR-CP dispersion is weighed. The total conductive polymer solids amount is
15 determined by multiplying the total dispersion weight by the solids content of the dispersion. Polyimide is added to the solvent dispersion so that the final weight ratio of the solids conductive polymer to polyimide is either 0.5/99.9, 1.0/99 or 2.5/97.5. The polyimide is added to an agitated TOR-CP keeping agitation with a magnetic stir bar.

20

Volume resistivity (ohm-cm) has been measured for films that contain 1,2.5 and 4% conductive polymer respectively. Figures 2 and 3 show measurements made on blends that contain the Triton AO resistant polyimide (TOR-NC) and a commercial polyimide from Ciba called Matramid.

25

Example 4- Analysis of Converted (Solvent Exchanged) Baytron™ P Batches

To better appreciate the performance characteristics of Baytron™ P formulation converted according to the invention, the following parameters were
30 analyzed: conductivity, viscosity, solids content, particle size and distribution, light transmission, pH value, density and water content. Analyses were performed according to recognized procedures. See Figures 4 and 5 ("MAV" numbers refer to specific Bayton™ P batches).

Referring now to the particle size analysis of Figures 4 and 5, the data shows an average particle size ranging from < 0.001 micron to >30 micron. Specifically shown by Figures 4 and 5 are particle analysis of three of samples, and then a
5 summary sheet showing several properties we are monitoring. Particle Size analysis was done by Micromeritics in Norcross GA. The technique used is called Eltone™ particle size analysis.

Figure 6 shows conductivity measurements using Baytron™ P (neat) and
10 batches of converted (solvent exchanged) Baytron™ P (MAV 92-96, 83-86 and 77). Resistances were measured according to standard procedures. The data show that the converted Baytron™ P formulations exhibited an increase in conductivity (decreased resistance) of about two to three orders of magnitude. Significantly, it has been found that the conductivity increase of the converted Baytron™ P formulation can be
15 achieved with a film thickness up to about half that of the neat formulation.

Example 5- Process For Making Conductive Films Useful In Antistat Applications

20 It is possible to combine the converted (solvent exchanged) TOR-CP solutions of this invention with a wide spectrum of suitable polymers e.g, polyimide, polycarbonate, epoxies, polyarylene ethers, polyester, PEN, and other solution processed polymers, using conventional film processing methods such as those disclosed herein. More specific examples of such polymers can be found in the
25 *Modern Plastics Encyclopedia* Vol. 75, No. 12 (Mid-November 1998 issue). Suitable procedures for blending the polymers and conductive polymer solution (TOR-CP) are known in the field including simple weight measurements, room temperature stirring, etc.

30 Two more specific methods for making the films are as follows.

A. Method 1

First, make a solution that essentially dissolves various polymer into the TOR-CP dispersion. Nearly any polymer that is soluble in the NMP solvent could be

used such as polyimide, polyesters, polyurethanes, polycarbonates, polysulfones, polyetherimides and the like. In one application, polymer was added to an agitated TOR-CP dispersion so that the ratio of conductive polymer to added polymer is in the range of 0.5% to 3% by weight. The solvent (NMP) content was then adjusted to bring the total solids content (conductive polymer/dopant plus non-conductive base polymer) to approximately 18%-22% by weight. The mixture was stirred until a homogeneous honey like consistency is achieved. The blended solution was then filtered through a 12 micron filter and cast onto a substrate using a drawdown bar, or lip casting process. The substrate was then passed through a heating section to drive off the NMP solvent at about 150C for 10-30 minutes depending on whether this is a continuous or batch process. This process has been practiced in both batch and continuous methods and various data has been collected.

B. Method 2

Another way to incorporate TOR-CP would be dependent on ability to convert the water based Baytron P into a high molecular weight polymer instead of into a solvent. A particular material of interest is polybutene (BP Amoco). Assuming the conductive polymer can be incorporated into the polybutene at about 50% concentration, then it will be possible to let that mixture down into polyolefins during a melt processing operation. This could then open up the possibility of making conductive polyethylene, or polypropylene with a much lower cost melt processing technique. The temperatures for processing this combination must be kept below 200C to prevent degradation to the conductive polymer dopant and this would be the case with polyolefins.

25

A preferred film produced by either of the foregoing specific methods is free standing and has a conductivity through the thickness (instead of just at the surface) which can be from <1 mil to >5 mils thick (1 mil = 0.001"). The volume resistance ranges from 10^4 - 10^{12} ohm-cm depending, for example, on the weight concentration of the conductive polymer. Particular applications for such films include antistatic packaging materials, electrostatic discharge (ESD) and electro-magnetic interference (EMI) shielding films.

30

The following materials were used, as needed, in the foregoing Examples unless specified otherwise.

- 22L Round Bottom 4 neck Flask (Ace Glass)
- Glas-Col Heating Mantle Canister
- 5 SGA Variac Controllers
- 19mm Glass Stir Shaft w/teflon paddle assembly (Ace Glass)
- 19mm Teflon Lined Stirrer Bearing (Ace Glass)
- Watson-Marlow Peristaltic Pump model #505DU
- Arrow 850 Stirrer Motor w/chuck
- 10 300mm Coil Condenser (Ace Glass)
- 325ml Dean Stark Trap (Aldrich)
- Teflon Coated Temperature Probe w/digital read
- Gilmont Instrument Nitrogen Flowmeter
- Nitrogen Bubbler
- 15 Model #T 25 Ultra-Turrax Disperser/Homogenizer (IKA-Works)

Example 6- Preparation of Polymer Coating Layers

- Table 2, below, shows a list of representative coatings produced during the
- 20 course of the present invention. Baytron-P, an aqueous based PEDOT:PSS conducting polymer manufactured and supplied by Bayer AG was used as a reference throughout the experiments. Tor-CP and Baytron-P coatings were fabricated by employing a spin-coating method with a 2000 rpm spin speed. Two and a half inch diameter and 1/16 inch thick borosilicate glass disks were used as substrates
- 25 throughout the experiments. Thickness of the final coatings was controlled by applying multiple spin-coating operations with the same spin speed and duration of spin of 10 seconds. After each spin coating, polymer coating/substrate combinations were dried by employing two different drying methods as described in Table 2: (1) oven dry at 80°C for 5 minutes and (2) dry at ambient temperatures for 60 minutes
- 30 followed by oven dry at 80°C for 5 minutes. All dried samples were stored in the sealed plastic bags before electrical conductivity/resistivity and optical transmission/absorbance measurements.

- More particularly, for spin-coating, the glass substrate was mounted on the vacuum chuck of the spinner and 1.5 mL of Tor-CP or Baytron-P solutions are applied in the middle of the substrate, followed by start spinning with the preset speed of 2000 rpm and duration of 10 seconds. Specific batch No. of the Tor-CP was
- 5 KAC79 and 0.6% solid content in NMP solvent. Baytron-P is 1.3% solid content in water solvent.

Thickness of the coating was measured using a stylus surface profilometer.

Table 2: Representative Coatings and Preparation Conditions

Coating ID	Conducting Polymers	Coating Thickness (nm)	Drying Conditions
Baytron-P-O1	Baytron-P	120	80C oven drying for 5 minutes
Baytron-P-O2	Baytron-P	314	80C oven drying for 5 minutes
Baytron-P-O3	Baytron-P	592	80C oven drying for 5 minutes
TOR-CP-O1	TOR-CP	52	80C oven drying for 5 minutes
TOR-CP-O2	TOR-CP	105	80C oven drying for 5 minutes
TOR-CP-O3	TOR-CP	171	80C oven drying for 5 minutes
TOR-CP-A1	TOR-CP	70	RT air dry for 60 minutes and followed by 80C oven drying for 5 minutes
TOR-CP-A2	TOR-CP	107	RT air dry for 60 minutes and followed by 80C oven drying for 5 minutes

5 Figures 9A-D are explained in more detail as follows. In particular, Figure 9A shows measured values of electrical resistivity of the resulting coatings as a function of coating thickness for Baytron-P and Tor-CP coatings. For Tor-CP coatings two different drying methods were employed as described in Table 2. Resistivity of these coatings was measured by employing a standard four point probe technique and

10 calculated for the known coating thickness and geometrical correction factor (ASTM Standard F374). Accuracy of the measured values of resistivity using four point probe method were confirmed by employing a Van der Pauw technique for the selected coating at outside laboratory.

15 As shown in Figure 9A for the given coating thickness, coatings from Tor-CP exhibited at least two orders of lower resistivity, higher electric conductivity, than that of Baytron-P coatings. For example, resistivity of the 105 nm thickness Tor-CP coating was 0.35 ohm-cm, while Resistivity of the 120 nm thickness Baytron-P coating was 162.74 ohm-cm. Furthermore, air/oven dried Tor-CP coatings exhibited

20 2-3 times lower resistivity than that of oven dried Tor-CP coatings. In air/oven dried Tor-CP coating, we measured Resistivity as low as 0.15 ohm-cm for coating thickness of 107 nm. There have been reports of lower Resistivity values than measured in the present example for the Baytron-P conducting polymer families. However, specific test conditions and coating process conditions are not clearly reported. Direct

comparison between externally reported values and our measured resistivity values for Baytron-P are not always accurate. Resistivity values for the Baytron-P coatings were used as a reference in the present invention when coatings of Baytron-P and Tor-CP were processed and measured same way.

5

It is significant that the air/oven dried coatings exhibited lower Resistivity than the oven dried coating, while other measured properties are appears to be same such as optical transmission/absorbance and surface morphology. Without wishing to be bound to theory, it is possible that the method impacts micro structural properties.

10

Coating samples made from Tor-CP or Baytron-P were intentionally exposed to uncontrolled laboratory conditions without any protection. About a month after, Resistivity of these samples was re-measured. While resistivities of the Tor-CP coating were remained the same (unchanged), Baytron-P coating became too soft.

15 Without wishing to be bound to any theory, it is possible that the Baytron-P reacts with moisture in the ambient atmosphere, and resistivity could not be determined by using the four point probe. This result clearly indicated that coatings of Tor-CP are substantially more stable than that of Baytron-P.

20 Treatment temperatures of up to about 200C have been achieved by oven drying. Substantially better results were not always seen.

See also Figure 12 providing resistivity and resistance data for selected TOR-CP and Baytron-P samples.

25

Example 7- Optical Transmission of TOR-CP and Baytron-P coatings

Figure 10 shows optical transmission of the Tor-CP and Baytron-P coatings, as a function of coating thickness, determined by UV-Vis-near IR dual beam differential spectrophotometer (Varian Model No. 2200). Black glass substrate (no coating on it) was used as a reference sample for each test, therefore, measured values of transmission/absorbance were coating layer properties only. Briefly, samples were scanned between 900 nm and 260 nm ranges with spectral bandwidth of 1 nm and scan rate of 1 nm/sec. As shown in Figure 10, optical transmission/absorbance

property is almost same for the coating of Tor-CP and Baytron-P for the given coating thickness. For a 105 nm thickness Tor-CP coating, transmission was above 90% wavelength ranges between 300 nm and 600 nm and it gradually dropped to 83% at 700 nm. A 120 nm thickness Baytron-P coating exhibited similar
5 transmission/absorbance characteristics in the same measurement.

Example 8- Preparation and Use of an OLED

Standard OLED devices, with Tor-CP or Baytron-P as a hole injection buffer
10 layer, were fabricated and characterized. See generally *Organic Light-Emitting Materials and Devices IV*, Kafafi, Z.H. Editor, in *Proceedings of SPIE*, vol. 4105 (2001) and references cited therein for disclosure relating to making and using standard OLED and related devices.

15 The specific device structure used in both cases was: ITO (150 nm) / Tor-CP or PEDOT:PSS / TPD (20 nm) / Alq₃ (40 nm) / LiF (0.5 nm) / Al (200 nm). As shown in Figure 11, OLED with Tor-CP reached a peak external quantum efficiency of 0.18% or a peak power efficiency of 1.08 lm/W at an applied bias of 5.10 V and a luminance of 8,790 cd/m². The maximum luminance of 32,000 cd/m² was obtained at
20 7.1 V. This compares to a similar water based PEDOT:PSS sample (heated at 50°C and dried in N₂) fabricated at the same time which had a peak external quantum efficiency of 0.15% or a peak power efficiency of 0.82 lm/W at an applied bias of 5.40 V and a luminance of 8,620cd/m². The water based (PEDOT) device had a maximum luminance of 14,700 cd/m² obtained at 7.0 V. The superior performance of
25 the Tor-CP in OLED devices suggests that improved electrical characteristics (for such applications) has been achieved. See also Figure 11.

As illustrated by this example, the OLED with the TOR-CP exhibited a better performance than the corresponding OLED with Baytron-P ITO.

30

Example 9 – Use of Tor-CP as an Electrode

Tor-CP can be used as an anode electrodes for display applications by replacing current industry standard of indium doped tin oxides (ITO). An example of this application is shown in Figures 13 and 14.

In Figure 13, measured surface resistance (in ohm/sq.) of the Tor-CP coating on 5 mil thickness PET substrate is shown as a function of number of spin coating layers. Baytron-P from Bayer A.G. was used as a reference material in this experiment. With two to three layer spin coatings, Tor-CP exhibited about 1-2 kohm/sq. surface resistance whereas Baytron-P exhibited about 100 kohm/sq. Optical transmission for the same set of coatings is above 86% and below 80% for Tor-CP and Baytron-P, respectively. Generally, for certain display applications, such as touch screen, anode electrode (currently ITO) should have surface resistance of less than 1-2 kohm/sq. and optical transmission of above 86%. Clearly, Tor-CP coatings can meet these requirements.

In addition, adhesion tests of these samples following Mil-C-4897A test protocol were also conducted. Results of this test indicated that Tor-CP exhibited very good adhesion rating of 4B, compared to very poor adhesion of Baytron-P on PET. Since the Tor-CP is in NMP, there is a surface mixing effect between Tor-CP and PET substrate whereas aqueous based Baytron-P may not have the mixing effect. The mixing effect between the Tor-CP and PET substrates at the interface would provide good adhesion.

Figure 15 shows data in support of Figures 13 and 14.

Example 10- Properties of Tor-CP and Baytron-P coatings

Resistivity/Conductivity of Tor-CP and Baytron-P coatings on glass substrates were determined by employing van der Pauw method in temperature ranges between 100-300 K. Thickness of the coatings used in this test were between 400-500 nm. Ln-Ln plots of the conductivity results are shown in Figures 16 and 17. As shown in these figures, Tor-CP coatings exhibited two orders higher conductivity than Baytron-P coatings in entire temperature ranges. In addition, Baytron-P coatings exhibited a kink at temperatures around 150 K whereas there is no kink in the plots of Tor-CP coatings. It is believed that the kink in the Ln-Ln plot of the conductivity indicated the changes in charge carrier transport mechanism in the Baytron-P coatings. No kink in the Tor-CP coatings probably implies solid charge carrier transport mechanism in

Tor-CP coatings and might attribute to the many orders higher mobility in the Tor-CP coatings.

5 **Example 10 – Solvent Exchange Process using Ethylene glycol as exchange solvent**

1. Place the Chem Glass 500 ml four neck round bottom flask into the oil bath.
2. Take the Ultra-Turrax disperser/ homogenizer model# T 25 equipped with 19
10 mm diameter shaft and place into the center neck of the 500 ml round bottom flask.
3. Hookup the temperature controller equipped with thermocouple to the oil bath.
4. Attach the Dean Stark Trap to the left neck of the 500 ml flask, then place 300
15 mm coil condenser on top of it. A tube will then run from the top of the condenser to the nitrogen bubbler.
5. In the right neck of the 500 ml flask, place the nitrogen line supplied by the Gilmont instruments flowmeter.
6. Add 100 ml Ethylene glycol into 500 ml flask.
7. In the front neck of the 500 ml flask, place the adapter with inner tubes
20 connected to the Watson-Marlow peristaltic pump.
8. Turn on the temperature controller and heat the solvent to 120°C under agitation from the Uita-Turrax T-25 homogenizer with speed at 20000 rpm. The speed setting should not need to be changed throughout the remainder of the process.
9. Set the Gilmont instruments nitrogen flowmeter to produce a steady flow of
25 nitrogen through the flask until it comes out the bubbler.
10. Using Watson-Marlow peristaltic pump, begin pumping 76 ml Baytron-P into the 500 ml flask at a flow rate of 1 ml/minute.
11. Continue pumping the Baytron-P into the 500 ml flask till complete (approx.
30 76 min)
12. As the Baytron-P is being fed into the 500 ml flask, water should start condensing and collecting in the Dean Stark Trap.
13. Increase the nitrogen flow considerably in order to force the water vapor up into the coil condenser.

14. The water will start to rapidly condense and collect in the Dean Stark Trap.
Drain the trap as needed.
15. Continue this process until the desired amount of water has been removed.
16. Turn off the temperature controller and the homogenizer, continue the
5 nitrogen flow till the product in the flask cool down to room temperature.
17. Remove the product from the flask.
18. The conductive coating will be made from the product using spin coating
method on glass substrate.
19. The surface resistances were measured with a Keithly 2000 4-point probe. The
10 bulk resistivity (ρ) was calculated using the equation below:
- $$\rho = (\pi * \text{thickness} * \text{surface resistance} * k) / \ln 2$$
- Where k = a correction factor based on the ratio of the probe to wafer diameter
and on the ratio of wafer thickness to probe separation.
20. Conductivity equal to the inverse of bulk resistivity
- 15 $\sigma = 1 / \rho$
21. Figure below shows that coatings from an Ethylene glycol solution , made by
solvent exchange , have a much lower surface resistance than Baytron-P
coating or have 300 times better conductivity.

20

Table 3: Solvent Exchange with Ethylene Glycol

Batch#	Baytron-P (V4071)	PG-02-44	PG-02-45	PG-02-49	PG-02-52	Pi
Quantity (ml)		176	176	176	176	
Solvent	water	ethylene glycol	ethylene glycol	ethylene glycol	ethylene glycol	e
Viscosity (cp)			171.5	570	1480	
Solid Content (%)	1.2	0.92	0.7	1.09	1.3	
Water Collected (ml)		66	41	78	92	
Solution Residue (ml)		94	117	81	68	
Thickness of the coating (nm)	85	70	50	90	130	
Surface Resistance(k-ohm/sq) 4-point	160	0.45	0.68	0.35	0.24	
Bulk resistivity (ohm cm) 4-point	25.808	0.060	0.065	0.060	0.059	
Conductivity(ohm cm) ⁻¹ 4-point	0.04	16.73	15.50	16.73	16.89	
Transmission on PET substrate		T = 86.5 % H = 0.71		T = 85.1% H = 1.18	T = 81 % H = 0.95	

5

All references disclosed in this application are incorporated herein by reference.

While the invention has been described with reference to specific
 10 embodiments, modifications and variations of the invention may be constructed
 without departing from the scope of the invention, which is defined in the following
 claims.

What is claimed is:

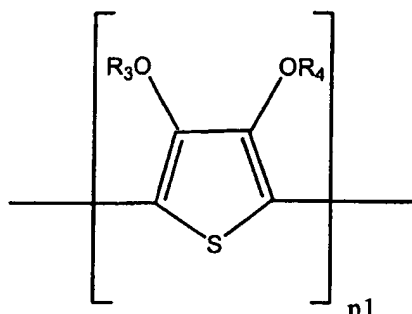
1. A method for exchanging solvent in a mixture comprising water and an optionally substituted polythiophene, the method comprising:

- 5 a) heating at least one solvent in a vessel under conditions suitable for vaporizing water,
- b) contacting the heated solvent with the mixture comprising water and optionally substituted polythiophene, the contact being sufficient to remove at least part of the water from the mixture as vapor; and
- 10 c) exchanging the water removed from the mixture with the solvent.
2. The method of claim 1, wherein the method further comprises removing the water vapor from the vessel.
- 15 3. The method of claims 1-2, wherein the boiling point of at least one of the solvents is at least about 100°C at standard temperature and pressure (STP).
4. The method of claims 1-3, wherein the boiling point of at least one of the solvents is between from about 100°C to about 250°C at standard temperature and pressure (STP).
- 20 5. The method of claims 1-4, wherein the solvent is heated in the vessel to at least about 100°C.
- 25 6. The method of claims 1-5, wherein the solvent is heated in the vessel to a temperature of between from about 100°C to about 250°C.
7. The method of claims 1-6, wherein the conditions further comprise exposing the solvent to a pressure of about 1 atmosphere in the vessel.
- 30 8. The method of claims 1-7, wherein the contacting step further comprises adding about 1 part of the mixture to at least about 2 parts heated solvent per minute.

- 5
9. The method of claims 1-8, wherein the contacting step further comprises adding about 1 part of the mixture to between from about 5 to about 10,000,000 parts heated solvent per minute.
10. The method of claims 1-9, wherein the contacting step further comprises adding the mixture to the heated solvent as a flow stream, aerosol; or a combination thereof.
- 10 11. The method of claim 10, wherein the addition of the mixture is continuous.
12. The method of claim 10, wherein the addition of the mixture is discontinuous.
- 15 13. The method of claim 12, wherein the mixture is added to the solvent as a discontinuous flow stream.
14. The method of claim 10, wherein the mixture is added to the solvent as drops.
- 20 15. The method of claims 1-14, wherein the contacting step further comprises dispersing the mixture along the surface of the heated solvent.
- 25 16. The method of claim 15, wherein the dispersal is configured to maximize contact between the mixture and the heated solvent.
17. The method of claims 1-16, wherein the contacting step further comprises adding the mixture below the surface of the heated solvent.
- 30 18. The method of claims 1-17, wherein the solvent is water soluble.
19. The method of claims 1-18, wherein the solvent is partially or fully insoluble in water.

- 5 20. The method of claims 1-19, wherein the solvent is a lower alkyl acetamide, lower alcohol including diols and triols, pyrrolidone, lower alkyl pyrrolidone, higher alkyl pyrrolidone, lower alkyl sulfoxide ; or a mixture thereof.
- 10 21. The method of claim 20, wherein the lower alkyl acetamide is dimethylacetamide (DMAC) and the lower alkyl pyrrolidone is N-methylpyrrolidone (NMP).
22. The method of claim 20, wherein the lower alcohol is ethylene glycol or glycerin.
- 15 23. The method of claim 20, wherein the lower alkyl sulfoxide is dimethylsulfoxide (DMSO).
24. The method of claims 2-23, wherein the water vapor removed from the mixture is a condensate or distillate.
- 20 25. The method of claim 24, wherein any water is removed from the mixture by the method.
26. The method of claims 1-25, wherein less than about 100% (w/v) of the water is removed from the mixture as vapor.
- 25 27. The method of claim 26, wherein between from about 25% (w/v) to about 100% (w/v) of the water is removed from the mixture.
28. The method of claim 26, wherein between from about 50% (w/v) to about 100% (w/v) of the water is removed from the mixture.
- 30 29. The method of claim 26, wherein between from about 1% (w/v) to about 95% (w/v) of the water is removed from the mixture as vapor.

30. The method of claim 1, wherein the polythiophene is represented by the following formula (II):



wherein R3 and R4 each independently represent hydrogen or a C1-C6 alkyl group, or together form an optionally substituted C1-C6 radical or a cyclohexylene-1,2 radical, and n1 is greater than 1.

31. The method of claim 30, wherein the polythiophene is associated with at least one polyanion.

32. The method of claim 31, wherein the polyanion is polystyrene sulfonic acid (PSS).

33. The method of claims 30-32, wherein R3 and R4 each independently represent C1-C4 alkyl or together form a C1-C4 radical.

34. The method of claim 33, wherein the C1-C4 radical is an ethylene 1,2 radical.

35. The method of claims 30-33, wherein n1 is less than about 10.

36. The method of claims 30-33, wherein n1 is less than about 5.

37. The method of claims 30-36, wherein the polythiophene is an optionally substituted poly-3,4-alkylene dioxathiophene.
38. The method of claim 37, wherein the polythiophene is poly-3,4-ethylene dioxathiophene.
39. The method of claims 1-38 wherein the mixture further comprises at least one additive.
40. The method of claim 39, wherein the additive is a binder.
41. A method for exchanging di-methylacetamide (DMAC) or N-methylpyrrolidone (NMP) or ethylene glycol for water in a colloidal water dispersion comprising poly-3,4-ethylene dioxathiophene present, the method comprising:
- a) heating an amount di-methylacetamide (DMAC) or N-methylpyrrolidone (NMP) or ethylene glycol in a first vessel to a temperature of between from about 100°C to about 250°C,
 - b) contacting the heated di-methylacetamide (DMAC) or N-methylpyrrolidone (NMP) or ethylene glycol with an amount of the colloidal water dispersion comprising water and poly-3,4-ethylene dioxathiophene, wherein the dispersion is added to the surface of the heated solvent at a rate of between from about 0.1 to about 1000 mls/minute, the contact being sufficient to remove at least part of the water from the dispersion as vapor; and
 - c) exchanging the water removed from the dispersion as vapor with the di-methylacetamide (DMAC) or N-methylpyrrolidone (NMP) or ethylene glycol.
42. The method of claim 41, wherein the method further comprises removing at least part of the water from the vessel as vapor.
43. The method of claims 41-42, wherein the method further comprises condensing the water in a trap.

44. The method of claims 41-43, wherein the method further comprises condensing the water vapor into a second vessel comprising at least one co-solvent.

5 45. The method of claims 41-44, wherein the ratio of the amount of the dimethylacetamide (DMAC) or N-methylpyrrolidone (NMP) or ethylene glycol to the amount of the mixture is more than one.

10 46. The method of claim 45, wherein the ratio is between from about 1.5 to about 10,000,000 or more.

47. The method of claim 46, wherein the ratio is between from about 2 to about 10.

15 48. The method of claims 1-47, wherein the method further comprises contacting the heated solvent with at least one non-reactive gas to facilitate removal of the water from the mixture.

20 49. The method of claim 48, wherein the gas is nitrogen, air, a noble gas; or a mixture thereof.

50. The method of claim 49, wherein the gas is pre-heated to about the temperature of the heated solvent.

25 51. The method of claim 50, wherein the co-solvent is di-methylacetamide (DMAC), N-methylpyrrolidone (NMP), ethylene glycol, acetonitrile, benzonitrile, methylcyanoacetate, dichloromethane; diethyl ether, dimethoxyethane; N,N-dimethylformamide, nitrobenzene, nitromethane, propionitrile, and propylene carbonate.

30 52. The method of claims 41-51, wherein less than about 100% (w/v) of the water is removed from the mixture.

53. The method of claim 52, wherein between from about 1% (w/v) to about 95% (w/v) of the water is removed from the mixture.
54. The method of claims 1-53, wherein the optionally substituted poly-3,4-alkylene dioxythiophene is provided as a colloidal water dispersion.
55. The method of claim 54, wherein the colloidal water dispersion further comprises at least one counter ion.
56. The method of claim 55, wherein the counter ion is polystyrene sulfonic acid and the optionally substituted poly-3,4-alkylene dioxythiophene is poly-3,4-ethylene dioxythiophene.
57. The method of claims 1-56, wherein the poly-3,4-ethylene dioxythiophene is commercially available as or Baytron™ P.
58. The method of claims 1-57 wherein the poly-3,4-ethylene dioxythiophene is a polymer derived from Baytron™ M.
59. The method of claims 1-58, wherein the contacting step further comprises subjecting the thiophene mixture to high sheer mixing sufficient to prevent or reduce agglomeration of the mixture.
60. The method of claim 59, wherein the high sheer mixing is provided by a homogenization or dispersion implementation.
61. A composition produced by any one of the methods of claims 1-60.
62. A composition comprising a poly-3,4-alkylene dioxythiophene; and between from about 1% (w/v) to about 100% (w/v) di-methylacetamide (DMAC) or N-methylpyrrolidone (NMP) or ethylene glycol.

63. The composition of claim 62, wherein the poly-3,4-alkylene dioxathiophene is associated with at least one polyanion.
- 5 64. The composition of claim 63, wherein the polyanion is polystyrene sulfonic acid (PSS).
65. The composition of claims 62-65, wherein the optionally substituted poly-3,4-alkylene dioxathiophene is poly-3,4-ethylene dioxathiophene commercially available as Baytron™ P.
- 10 66. The composition of any one of claims 62-65 further comprising at least one additive.
67. The composition of claim 66, wherein the additive is a binder.
- 15 68. The composition of claim 66, wherein the additive is ferric toluene sulfonic acid (Baytron™ C).
69. The composition of claim 68, wherein the ferric toluene sulfonic acid is present in trace amounts.
- 20 70. The composition of claim claims 62-69, wherein the composition has at least an order of magnitude higher conductivity than the corresponding unexchanged thiophene mixture.
- 25 71. The composition of claim 70, wherein the composition comprises a converted (solvent exchanged) polydioxathiophene and the unexchanged thiophene mixture is Baytron™ P.
- 30 72. The composition of claim 71, wherein the solvent exchanged polydioxathiophene (converted Baytron P) includes at least one of NMP or DMAC or ethylene glycol.

73. A conductive coating comprising the composition of any one of claims 62-72 configured as a layer having a surface resistance of between from about 10 to about $10^{12} \Omega/\text{sq}$.
- 5 74. The coating material of claim 73 having between from about 1 mg/m^2 to about 500 mg/m^2 of the composition in the layer.
75. The coating of claim 74 in which the layer has an optical density of between from about 0.0001 to about 0.05 at between from about 300nm to about 700nm.
- 10
76. The coating material of claim 75, wherein the layer has a light transmission of between from about 10% to about 99% as measured by a BYK Gardner Haze-gard plus machine.
- 15
77. The coating material of claim 76, wherein the layer has a light transmission of between from about 80% to about 95% as measured by a BYK Gardner Haze-gard plus machine.
- 20
78. A conductive film comprising the composition of any one of claims 62-65 and at least one polymer, co-polymer, graft polymer; or blend thereof.
79. The conductive film of claim 78 configured as a layer having a surface resistance of between from about 10 to about $10^{12} \Omega/\text{sq}$.
- 25
80. The conductive film of claims 78-79 having between from about 1 mg/m^2 to about 500 mg/m^2 of the composition in the layer.
81. The conductive film of claims 78-80 in which the layer has an optical density of between from about 0.0001 to about 0.05 at between from about 300nm to about 700nm.
- 30

82. The conductive film of claims 78-80, wherein the layer has a light transmission of between from about 80% to about 95% as measured by a BYK Gardner Haze-gard plus machine.
- 5 83. The conductive film of claims 78-82 further comprising the polymer, wherein the weight ratio of the converted (solvent exchanged) polydioxothiophene to the polymer is about 10:90 to about 0.1:99.9.
- 10 84. The conductive film of claim 83, wherein the weight ratio of the converted (solvent exchanged) polydioxothiophene to the polymer is about 6:94 to about 0.5:99.5.
85. The conductive film of claims 78-84, wherein the polymer is a polyimide.
- 15 86. The conductive film of claim 85, wherein the polyimide is TOR-NC.
87. The conductive film of claims 78-86, wherein the converted polydioxothiophene is Baytron™ P.
- 20 88. An article of manufacture comprising the composition, coating or film of any one of claims 61-87.
89. The article of manufacture of claim 79, wherein the article is one of an antiradiation coating, antistatic coating, battery, catalyst, deicer panel, electrochromic
25 window, electrochromic display, electromagnetic shielding, electromechanical actuator, electronic membrane, embedded array antenna, fuel cell, infrared reflector, intelligent material, junction device (PV), lithographic resist, non-corrosive paint, non-linear optical device, conductive paint, polymer electrolyte, radar dish, redox capacitor, sealant, semiconductor circuit, sensor, smart window, telecom device,
30 waveguide, or wire (low current).
90. The article of manufacture of claim 89, wherein the electromechanical actuator is one of a biomedical device, micropositioner, microsorter, microtweezer, or microvalve.

91. The article of manufacture of claim 89, wherein the sensor is one of a biological, chemical, electrochemical, irradiation dosage, mechanical shock, temperature, temperature limit, or time-temperature sensor.

5

92. A method for making an electronic implementation, the method comprising:

- a) contacting at least one of the compositions, coatings or film of claims 61-87 with a first polymer layer,
- 10 b) dissolving at least a portion of the first polymer layer with the composition under conditions forming a hole in the first polymer layer; and
- c) evaporating the solvent in the composition to make the electronic implementation.

15

93. The method of claim 92, wherein at least step a) of the method is repeated at least once to make the electronic implementation.

94. The method of claims 92-93, wherein steps a), b) and c) are repeated
20 twice or more to print the electronic implementation.

95. The method of claims 92-94, wherein the hole (via-hole or interconnect) comprises a first end contacting the first polymer layer and a second end contacting a substrate layer.

25

96. The method of claim 95, wherein the hole is substantially filled with the composition.

97. The method of claims 92-96, wherein at least step a) of the method is
30 performed using a standard ink-jet printer.

98. The method of claim 97, wherein the ink-jet printer comprises at least two nozzles, each nozzle comprising the same or different composition.

99. The method of claims 92-98, wherein at least one of the compositions comprises poly(3,4-ethylenedioxy-thiophene).

100. The method of claim 99, wherein the composition further comprises
5 polystyrene sulfonic acid (PEDOT/PSS).

101. The method of claim 99, wherein the composition is Baytron™-P or a polymer of Baytron™-M.

102. The method of claims 92-101, wherein the first polymer layer comprises
10 or consists of a dielectric polymer.

103 The method of claim 102, wherein the dielectric polymer is
polyvinylphenol.
15

104. The method of claims 92-103, wherein the substrate layer is insoluble in
the solvent of the composition.

105. The method of claim 104, wherein the substrate layer is organic and
20 flexible, or organic and rigid.

106. The method of claim 104, wherein the substrate layer is a polyimide.

107. An electronic implementation produced by the methods of claims 92-
25 106.

108. The electronic implementation of claim 107, wherein the implementation
is an inverter capable of converting a high-voltage input to a low-voltage output; or a
low-voltage input to a high-voltage output.
30

109. The electronic implementation of claim 108, wherein the inverter is a
component of an electronic circuit which circuit comprises at least one source
electrode and at least one drain electrode.

110. The electronic implementation of claim 109, wherein the source and drain electrodes are separated from each other by about 1 to 10 micrometers.

5 111. The electronic implementation of claims 109-110, wherein the electronic circuit has an output between from about -20V to about 0V.

112. The electronic implementation of claim 109-111, wherein the electronic circuit has an input between from about 0V to about -20V.

10

113. An article of manufacture comprising the electronic implementation of claims 107-112.

114. The article of manufacture of claim 113, the article being a liquid crystal
15 display, electrophoretic ink display, polymer disperse liquid crystal (PDLC) or an identification tag.

115. The article of manufacture of claim 114, wherein the identification tag is a smart label adapted for use in consumer good.

20

116. The article of manufacture of claim 115, wherein the consumer good is a toy or supermarket item.

117. Optically transparent and electrically conductive polymeric coatings,
25 which are fabricated using organic solvent based conducting polymers of poly(ethylenedioxythiophene):poly(styrene sulfonic acid) (PEDOT:PSS) families, of which environmental stability, low water content, low water affinity and flexibility are important consideration for electro-optic device applications.

30 118. The conductive polymeric coatings according to claim 117, where in said coatings exhibited resistivities less than 1 ohm-cm and optical transmission greater than 90% in wavelength ranges between 300 nm and 600 nm for the coating thickness about 107 nm.

119. Methods of fabricating the conductive polymeric coatings according to claim 117, where in said coatings is produced by employing controlled drying processes of air dry for one hour at ambient temperatures followed by oven dry at 80°C for 5 minutes to improve electrical conductivity without degrading optical transmission.

120. Electro-optic devices manufactured utilizing the conductive coatings according to claim 117.

121. Electro-optic devices manufactured utilizing the coating fabrication method according to claim 119.

122. The method of claims 1-60, wherein the methods further comprise, after step c), forming a coating composition from the mixture and subjecting the composition to at least one drying treatment step.

123. The method of claim 122, wherein the drying treatment step comprises subjecting the coating composition to a temperature of from between about room temperature (25 °C) to about 200 °C for less than about a day (24 hours).

124. The methods of claims 122-123, wherein the method comprises at least two drying treatment steps the same or different.

125. The method of claims 122-124, wherein the coating composition is subjected to a drying treatment of from between about 50 °C to about 150 °C for less than about 12 hours.

126. The method of claims 122-125, wherein the coating composition is subjected to a drying temperature of about 80 °C for less than about 5 hours.

127. The method of claims 122-126, wherein the coating composition is subjected to a drying temperature of about 80 °C for about 1 hour or less.

128. The method of claim 127, wherein the coating composition is subjected to the drying temperature for between from about 1 to about 15 minutes.

129. The method of claims 122-128, wherein the drying treatment step
5 comprises subjecting the coating composition to room temperature (25 °C) for less about two hours or less followed by treatment at about 80 °C for between from about 1 to about 15 minutes.

130. The method of claims 122-129, wherein the coating composition has a
10 thickness of from between about 50nm to about 1000nm.

131. The method of claim 130, wherein the coating composition has a thickness of from between about 60nm to about 750nm.

132. A composition produced from any one of the methods of claims 122-
131.

133. A conductive coating comprising the composition of claims 61-87 and 132 configured as a layer having a resistivity of between from about 0.01 to about (ohm-cm) and a thickness of between about 10nm to about 250 nm.

20 134. A conductive coating comprising the composition of claims 61-87 and 132 configured as a layer having a surface resistance of between from about 10 to about 10,000 (ohm/sq) and a thickness of between about 10nm to about 250 nm.

25 135. A conductive coating comprising the composition of claims 61-87 and 132 configured as a layer having an optical transmission of at least about 90% between about 300nm and 600nm wavelengths.

30 136. A conductive coating comprising the composition of claims 61-87 and 132 configured as a layer having at least one of the following characteristics: 1) a resistivity of between from about 0.01 to about 1 (ohm-cm); 2) a surface resistance of between from about 10 to about 10,000 (ohm/sq); 3) a thickness of between about 10nm to about 250 nm; and 4) an optical transmission of at least about 85% between about 300nm and 600nm wavelengths.

137. An article of manufacture comprising the composition, coating or film of any one of claims 132-136.

5 138. The article of manufacture of claim 137, wherein the article comprises or consists of at least one electro-optical implementation.

139. The article of manufacture of claims 137-138, wherein the electro-optic implementation is an organic light emitting device (OLED).

10

140. An organic light emitting device (OLED) comprising at least one of the following components operatively linked together: 1) metal cathode; 2) electron transport layer (ETL); 3) organic emitter; 4) hole injection layer (HIL); and 5) a glass substrate layer.

15

141. The OLED of claim 140 further comprising an indium doped tin oxide (ITO) anode.

142. The OLED of claim 140, wherein the HIL layer comprises at least one
20 of the compositions of claims 53-78, 123-126.

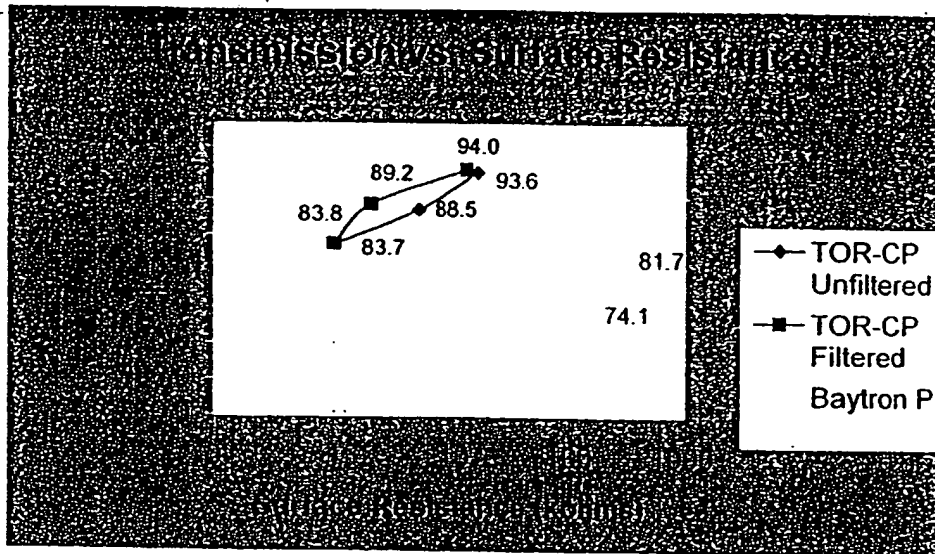
143. The OLED of claims 140-142, wherein the OLED has a peak external quantum efficiency of between about 0.02% to about 0.2% at between from about 4 to about 8 volts.

25

144. The OLED of claim 143, wherein the OLED has a peak power efficiency of between from about 0.5 to about 2 lm/W at an applied bias of between from about 1 to about 8 volts.

30 145. The OLED of claim 144, wherein the OLED has a luminance of about 7000 to about 9000 cd/m².

146. The OLED of claims 140-145, wherein the OLED has a maximal luminance of between from about 10,000 to about 50,000 cd/m^2 at about 4 to about 8 volts.

**Figure 1**

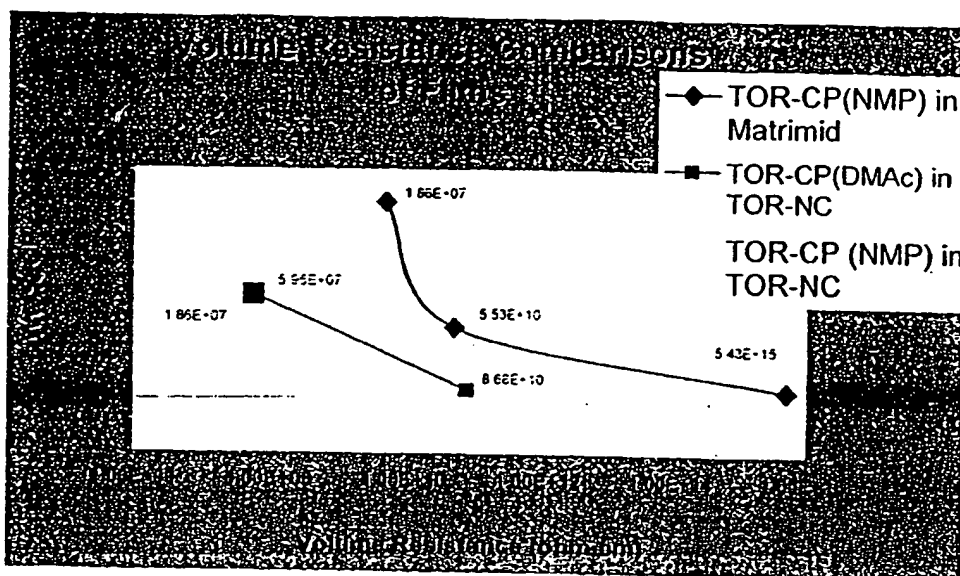


Figure 2

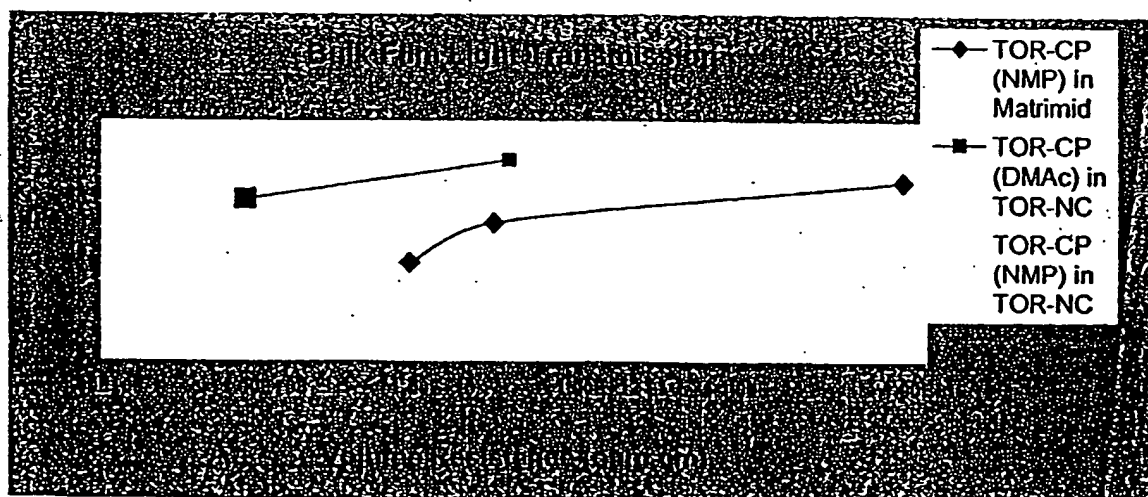


Figure 3

Batch #	MAV2-72	MAV2-77	MAV2-79	MAV2-80	MAV2-81	MAV2-82	MAV2-84	MAV2-83
Quantity	22L	22L	5L	1L	5L	5L	22L	5L
Solvent	NMP	NMP	NMP	DMAc	NMP	NMP	NMP	NMP
Conductivity	$S = 4.77 \times 10^7$ ohm/sq $V = 3.60 \times 10^3$ ohm-cm	$S = 2.91 \times 10^8$ ohm/sq $V = 1.86 \times 10^3$ ohm-cm	Ohm2 = 0.02-0.04 MOhm Ohm4 = 0.003-0.005 MOhm	Ohm2 = 0.009-0.01 MOhm Ohm4 = 0.0015 MOhm	Ohm2 = 0.02-0.04 MOhm Ohm4 = 0.005 MOhm	Ohm2 = 0.02-0.04 MOhm Ohm4 = 0.002-0.005 MOhm	Ohm2 = 0.1-0.3 MOhm Ohm4 = 0.03-0.04 MOhm	Ohm2 = 0.005-0.01 MOhm Ohm4 = 0.002 MOhm
Viscosity-Brookfield (spindle #2 @100 rpm) 25C	40 cP	48 cP	51 cP	50 cP	51 cP	42 cP	51 cP	45 cP
Solids Content oven temp. 210C	0.52%	0.384%	0.924%	1.554%	0.951%	0.986%	0.477%	0.549%
Particle size and distribution	1.1 um	19.0 um	14.5 um	5.6 um	11.6 um	14.8 um	8.0 um	35.9 um
Transmission 5% TOR-CP	T = 28.8% H = 0.48%	T = 32.0% H = 0.22%	T = 12.3% H = 1.40%	T = 0.22% H = 13.5%	T = 13.2% H = 1.46%	T = 14.9% H = 1.18%	T = 25.0% H = 0.78%	T = 25.8% H = 0.40%
Ph Value	4.91	4.97	4.04	6.61	3.94	3.45	4.95	4.30
Density	1.037 g/cc	1.036 g/cc	1.033 g/cc	0.956 g/cc	1.034 g/cc	1.034 g/cc	1.034 g/cc	1.034 g/cc
Water Content	6.13%	4.90%	0.64%	5.75%	0.74%	1.42%	2.19%	0.37%

Figure 4

Batch #	MAV2-85	MAV2-86	MAV2-89	KAC2-167	MAV2-87	MAV2-88	MAV2-90	KAC3-
Quantity	22L	5L	5L	5L	From lot 77	From lot 79	5L	5L
Solvent	NMP	NMP	NMP	NMP			NMP	NMP
Conductivity	Ohm2 = 0.01-0.04 MOhm Ohm4 = 0.005-0.01 MOhm	Ohm2 = 0.01 MOhm Ohm4 = 0.001 MOhm	Ohm2 = 0.03-0.04 MOhm Ohm4 = 0.004-0.005 MOhm	Ohm2 = 0.02-0.06 MOhm Ohm4 = 0.004-0.007 MOhm				
Viscosity-Brookfield (spindle #2 @100 rpm) 25C	42 cP	61 cP	64 cP	38 cP				
Solids Content oven temp. 210C	0.378%	0.428%	0.664%	0.622%			0.904%	0.935%
Particle size and distribution	42.5 um	8.3 um						
Transmission 5% TOR-CP	T = 40.0% H = 0.20%	T = 21.5% H = 0.72%	T = 17.9% H = 0.89%	T = 35.2% H = 0.18%				
Ph Value	2.85	3.30	3.37	3.35				
Density	1.032 g/cc	1.038 g/cc	1.037 g/cc	1.033 g/cc				
Water Content	1.57%	3.83%						

Figure 5

Drawdown conductivity measurements

Sample ID	% solids	Wet Film thickness	Calculated dry film thickness (0.7 x Wet thickness) x (% solids)	Measured resistance with ohmmeter	4 point probe resistance (ohm/4 scale)	Appearance
MAV2-92	0.55	120 micron	0.46 micron	1637 Ω /sq, 1828 Ω /sq, 1504 Ω /sq	0.5K 0.8K 0.7K	Smooth
MAV2-93	0.48	120 micron	0.40 micron	84K Ω /sq 94K Ω /sq	0.025M 0.022M	Smooth
MAV2-94	0.38	120 micron	0.32 micron	11K Ω /sq 5K Ω /sq 10K Ω /sq	3K 2.6K 1.7K 2K	Smooth
MAV2-95	0.43	120 micron	0.36 micron	1200 Ω /sq 1600 Ω /sq	0.63K 0.6K 0.73K	Smooth
MAV2-96	0.62	120 micron	0.52 micron	13K Ω /sq 13K Ω /sq 17K Ω /sq 18K Ω /sq	6K 6.1K 5.4K 6K	Smooth
MAV2-83	0.55	120 micron	0.46 micron	4290 Ω /sq 2429 Ω /sq	0.86K 0.78K 1.5K	Segregated
MAV2-84	0.48	120 micron	0.40 micron	12.7K Ω /sq 18.2K Ω /sq	5.2K 8.0K 4.3K	Smooth
MAV2-85	0.38	120 micron	0.32 micron	158K Ω /sq 1400M Ω /sq	---	Segregated
MAV2-86	0.43	120 micron	0.36 micron	1200 Ω /sq 2600 Ω /sq	0.5K 0.51K 0.5K	Smooth
MAV2-77	0.38	120 micron	0.52 micron	1776 Ω /sq 1915 Ω /sq	0.74K 0.61K 0.63K	Grainy
Baytron P	1.3	120 micron	1.09 micron	76K Ω /sq 65K Ω /sq 96K Ω /sq	31K 21K 30K	Smooth
Baytron P	1.3	60 micron	0.54 micron	114K Ω /sq 128K Ω /sq 124K Ω /sq	0.05M 0.05M 0.05M	Smooth
Baytron P	1.3	30 micron	0.27 micron	48K Ω /sq 43K Ω /sq 59K Ω /sq	0.02M 1.5M 0.01M 2.5K	Smooth
Baytron P	0.5	120 micron	0.42 micron	37K Ω /sq 157K Ω /sq 46K Ω /sq	1M 7M 0.3M	Smooth
Baytron P	0.5	60 micron	0.21 micron	38K Ω /sq 33K Ω /sq 34K Ω /sq	1.1M 0.01M 0.01M 0.01M	Smooth
Baytron P	0.5	30 micron	0.10 micron	103K Ω /sq 105K Ω /sq	22K 0.8M 30M	Smooth

Figure 6

Date	MAV2-72	MAV2-77	MAV2-79	MAV2-80	MAV2-81	MAV2-82	MAV2-84	MAV2-83	MAV2-85
Quantity	22L	22L	5L	1L	5L	5L	22L	5L	22L
Solvent	NMP	NMP	NMP	DMAc	NMP	NMP	NMP	NMP	NMP
Conductivity	$S = 4.77 \times 10^{-8} \text{ cm/mq}$	$S = 2.91 \times 10^{-8} \text{ cm/mq}$	$S = 0.02 \text{ g/cc}$	$S = 0.005 \text{ g/cc}$	$S = 0.02 \text{ g/cc}$	$S = 0.02 \text{ g/cc}$	$S = 0.02 \text{ g/cc}$	$S = 0.02 \text{ g/cc}$	$S = 0.02 \text{ g/cc}$
Viscosity (cP)	$\eta = 2.60 \times 10^{-3} \text{ g/cc-cp}$	$\eta = 1.66 \times 10^{-3} \text{ g/cc-cp}$	$\eta = 0.005 \text{ g/cc-cp}$	$\eta = 0.001 \text{ g/cc-cp}$	$\eta = 0.005 \text{ g/cc-cp}$	$\eta = 0.005 \text{ g/cc-cp}$	$\eta = 0.005 \text{ g/cc-cp}$	$\eta = 0.005 \text{ g/cc-cp}$	$\eta = 0.005 \text{ g/cc-cp}$
Boiled in 200 mL	40 cP	48 cP	51 cP	50 cP	51 cP	42 cP	51 cP	45 cP	42 cP
Solids Content	0.52%	0.38%	0.92%	1.55%	0.95%	0.99%	0.48%	0.55%	0.38%
Particle size and distribution	1.1 um	19.0 um	14.5 um	5.6 um	11.6 um	14.8 um	8.0 um	35.9 um	42.3 um
Translucence %	T = 28.8%	T = 32.0%	T = 12.3%	T = 0.22%	T = 13.2%	T = 14.9%	T = 25.8%	T = 25.8%	T = 40.0%
TOH-CF	H = 0.48%	H = 0.32%	H = 1.40%	H = 13.5%	H = 1.46%	H = 1.18%	H = 0.78%	H = 0.40%	H = 0.20%
Pz Value	4.91	4.97	4.04	6.61	3.94	3.45	4.93	4.5	2.85
Density	1.037 g/cc	1.036 g/cc	1.033 g/cc	0.936 g/cc	1.034 g/cc	1.034 g/cc	1.034 g/cc	1.034 g/cc	1.032 g/cc
Water Content	6.13%	4.90%	0.64%	5.73%	0.74%	1.42%	2.19%	0.37%	1.57%
Drawdown surface resistance (mV)	1236 Ω/sq	1845 Ω/sq	2660 Ω/sq		2150 Ω/sq	3720 Ω/sq	13500 Ω/sq	33600 Ω/sq	77900 Ω/sq

Figure 7A

MAV2-86	MAV2-89	KAC2-167	MAV2-87	MAV2-88	MAV2-90	KAC3-26	MAV2-91	KAC3-40	MAV2-92
SL	SL	SL	From lot 77	From lot 79	SL	SL	SL	SL	From lot 83
			Fluidized	Fluidized					Fluidized
NMP Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm	NMP Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm	NMP Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm	NMP Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm	NMP Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm	NMP Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm	NMP Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm	NMP Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm	NMP Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm	NMP Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm Q _{max} = 0.01 MOhm Q _{min} = 0.001 MOhm
61 cP	61 cP	38 cP			48 cP	45 cP	54 cP	64 cP	
0.43%	0.66%	0.63%	0.33%	0.92%	0.90%	0.94%	0.62%	0.77%	0.55%
8.3 um	2.4 um	33.7 um	0.21 um	1.14 um	20.8 um	21.5 um	24.8 um	6.6 um	0.34 um
T = 21.5% R = 0.72% 3.5	T = 17.9% R = 0.89% 3.7	T = 33.2% R = 0.18% 3.3			T = 19.2% R = 1.09% 3.49	T = 24.3% R = 1.09% 3.32	T = 17.3% R = 1.41% 3.68	T = 13.5% R = 1.06% 3.74	
1.038 g/cc	1.037 g/cc	1.033 g/cc			1.035 g/cc	1.034 g/cc	1.035 g/cc	1.034 g/cc	
1.03%	1.03%	0.83%			0.51%	0.20%	1.48%	2.3%	
1900 Ω/μ	4040 Ω/μ	29,000 Ω/μ	1880 Ω/μ	13,625 Ω/μ	24,000 Ω/μ	24710 Ω/μ	3100 Ω/μ	10,000 Ω/μ	16500 Ω/μ

Figure 7B

MAV2-93	MAV2-94	MAV2-95	MAV2-96	MAV2-97	MAV2-99	MAV2-100
From lot 84	From lot 85	From lot 86	From lot KAC2-167	From lot 77		111201
Fluidized	Fluidized	Fluidized	Fluidized	Fluidized - 1 pass		
NMP	NMP	NMP	NMP	NMP		NMP
Q _{test} = 0.1-0.2	Q _{test} = 0.1-0.2	Q _{test} = 0.01-0.03	Q _{test} = 0.05-0.08	Q _{test} = 0.023 MOhm		
MOhm	MOhm	MOhm	MOhm	MOhm		
Q _{test} = 0.1-0.2	Q _{test} = 0.1-0.2	Q _{test} = 0.001-0.003	Q _{test} = 0.007 MOhm	Q _{test} = 0.0023 MOhm		
MOhm	MOhm	MOhm				
0.18%	0.18%	0.43%	0.62%	0.38%		5% 77
0.60 um	0.63 um	0.79 um	0.11 um	0.63 um		
39,000 Ω/mq	9,000 Ω/mq	1,400 Ω/mq	13,250 Ω/mq	18,770 Ω/mq	19,300 Ω/mq	190 Ω/mq for 4 micron film 421 Ω/mq for 2 micron film 470 Ω/mq for 1 micron film

Figure 7C

Formulation Performance Table

Triton ID	Conductive component	Date Measured	Surface resistance (Ohms/sq)	Thickness	Comments
MAV2-87-1	TOR-CP		0.62 M Ohm 620K		
MAV2-87-2	TOR-CP		0.42 M Ohm 420K		
MAV2-87	TOR-CP		0.81 M Ohm 810 K		1 layer 1 ml wet
MAV2-87	TOR-CP		48 K		2 layers 1 ml wet
MAV2-77	TOR-CP		No reading		1 layer 1 ml wet
MAV2-77	TOR-CP		No reading		2 layers 1 ml wet

Figure 8

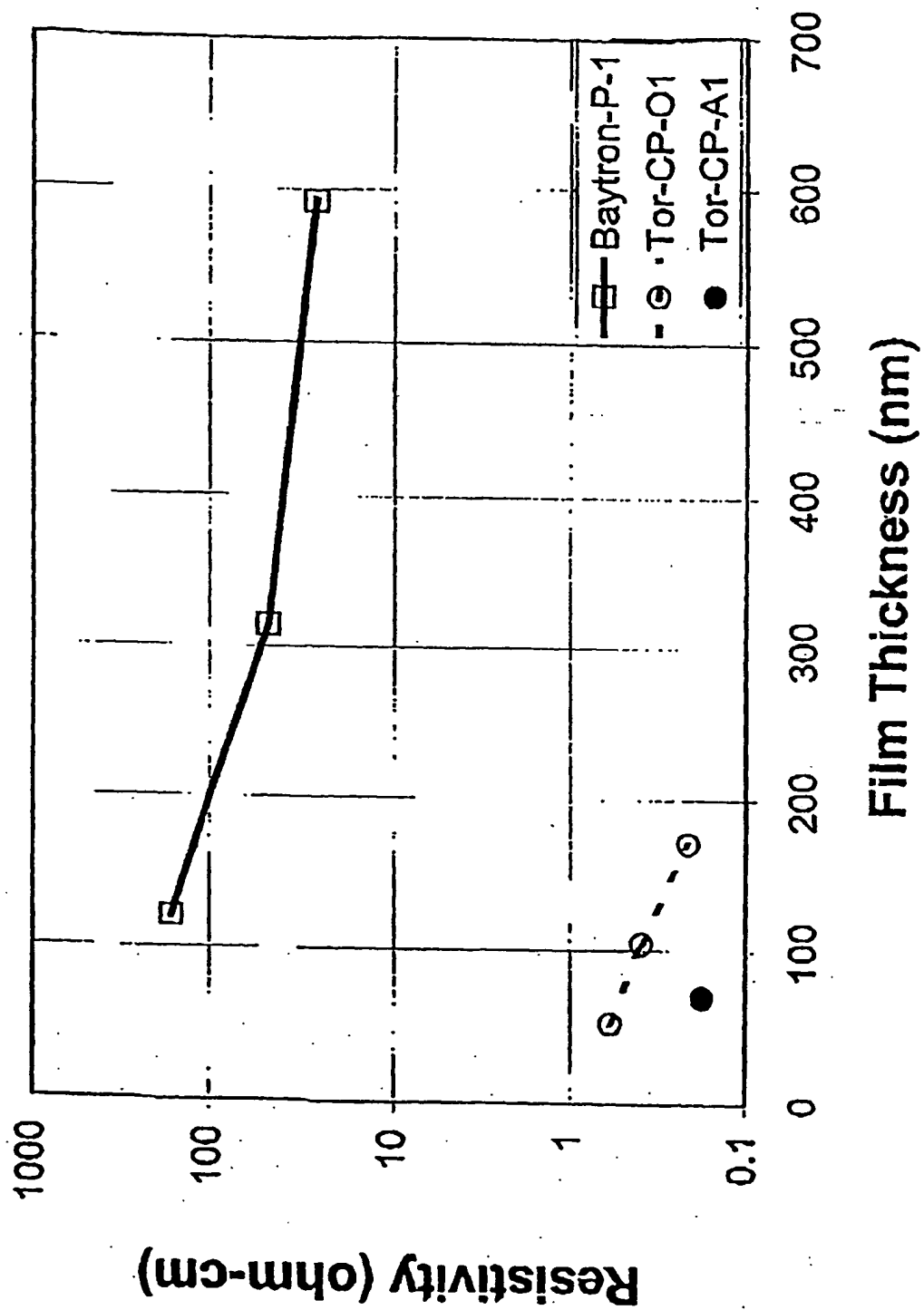


Figure 9A

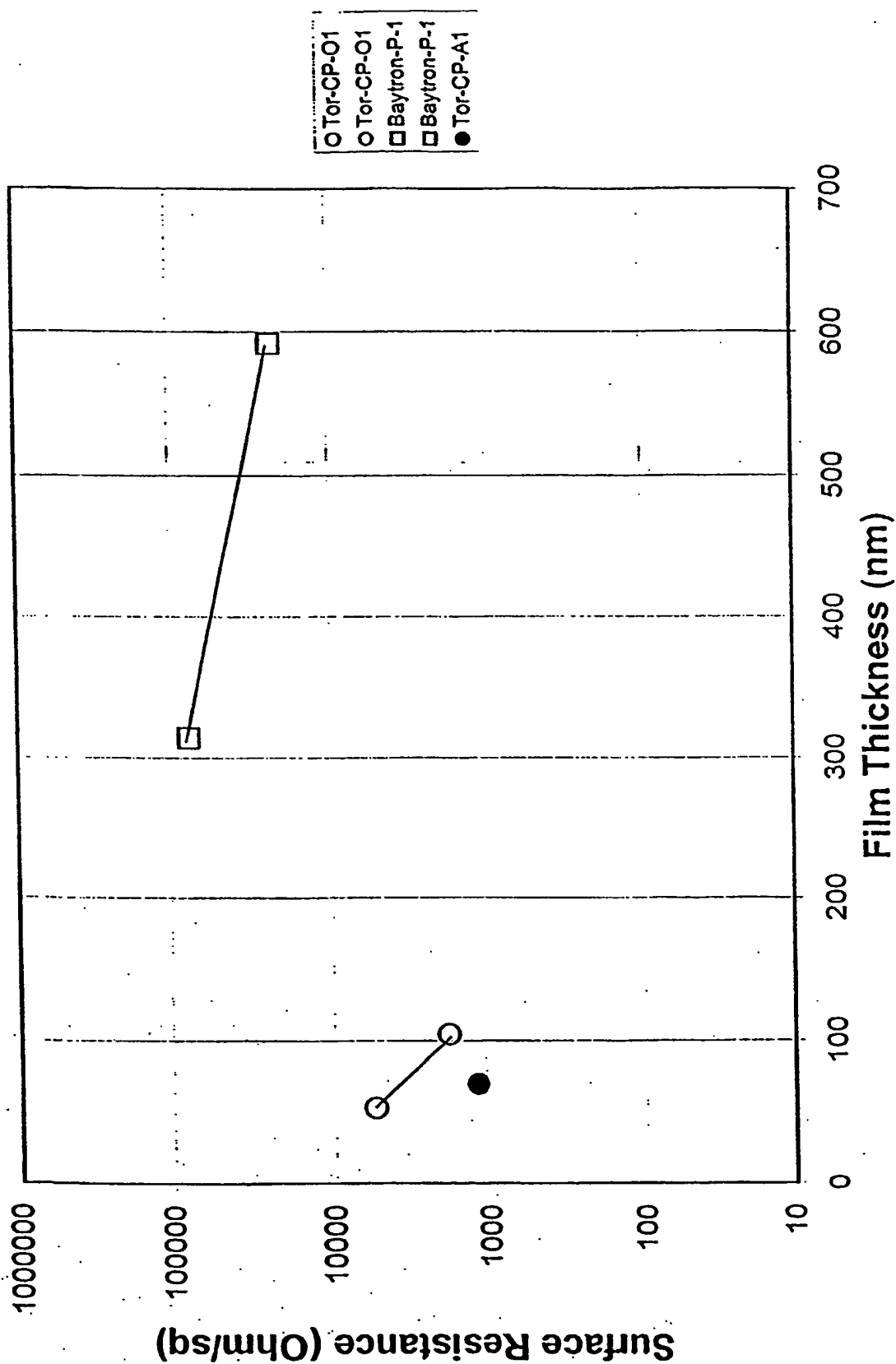


Figure 9B

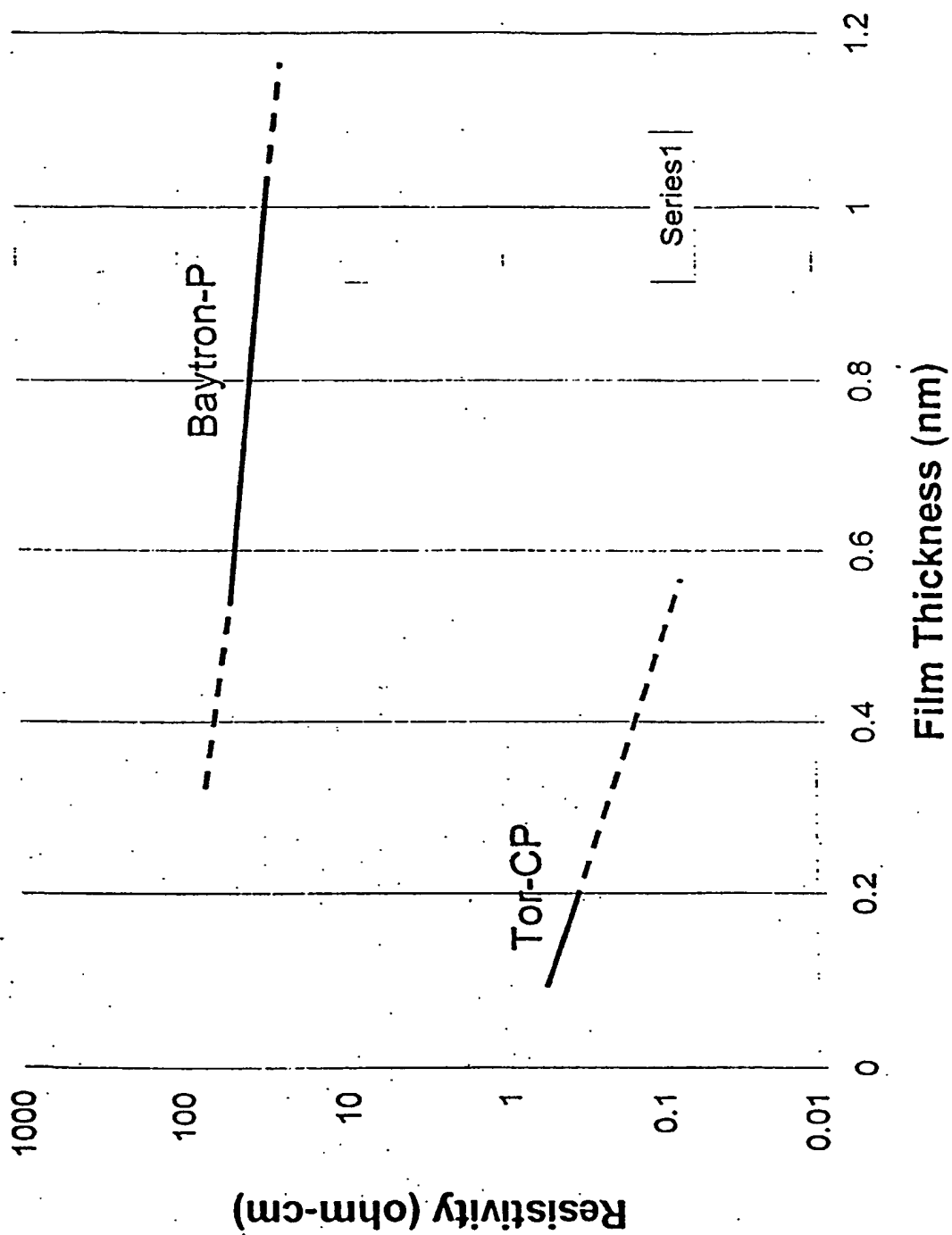


Figure 9C

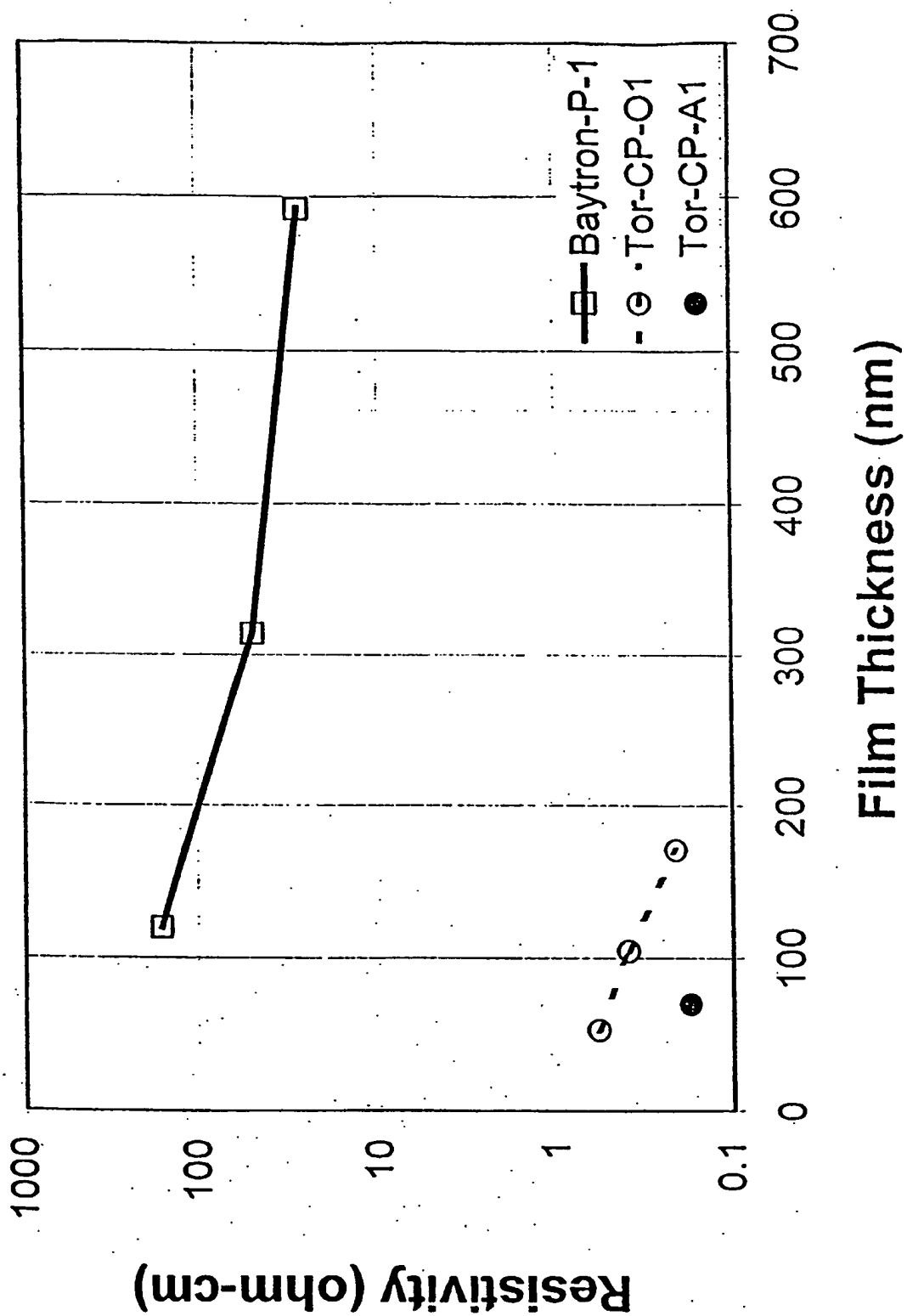


Figure 9D

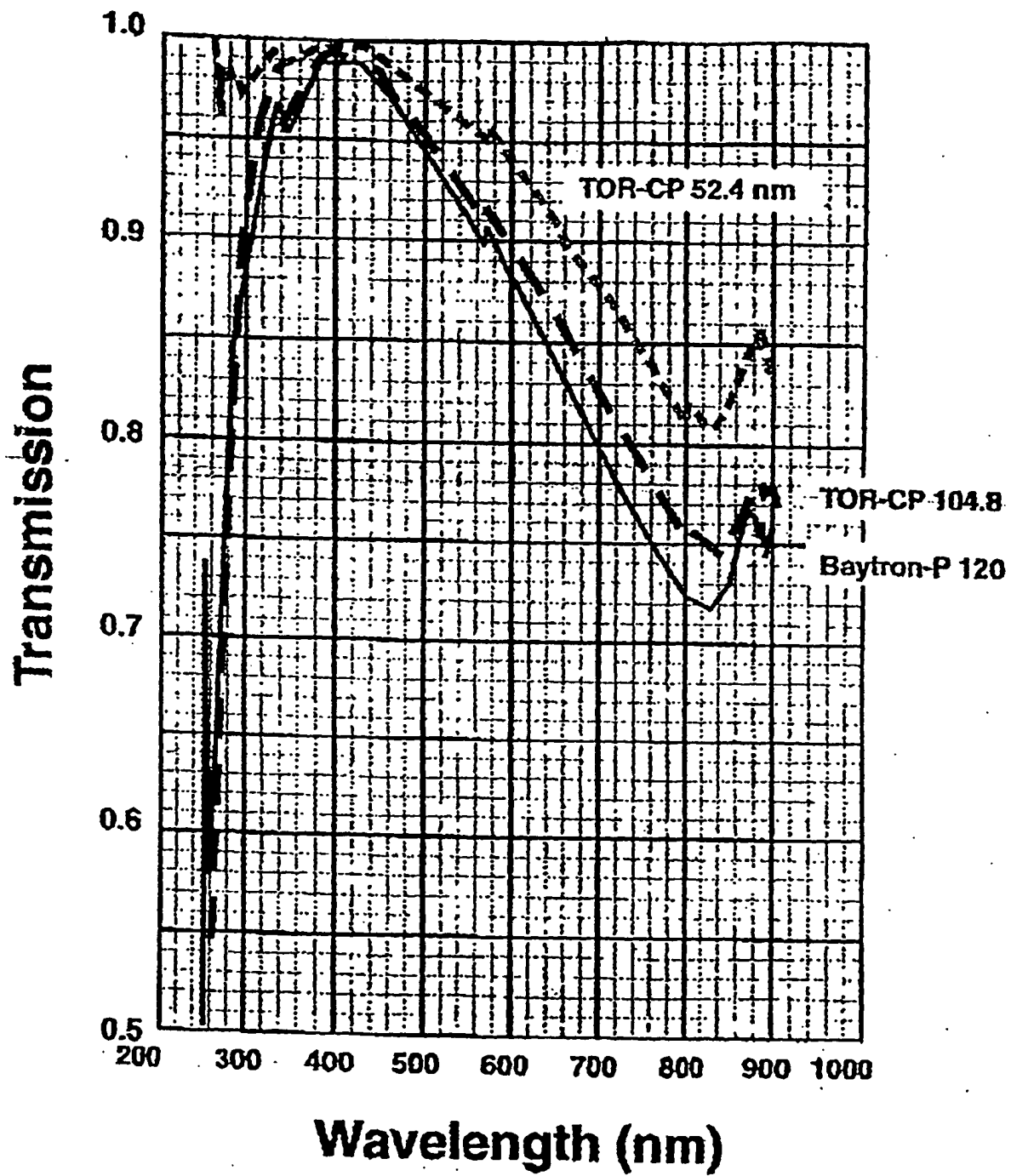


Figure 10

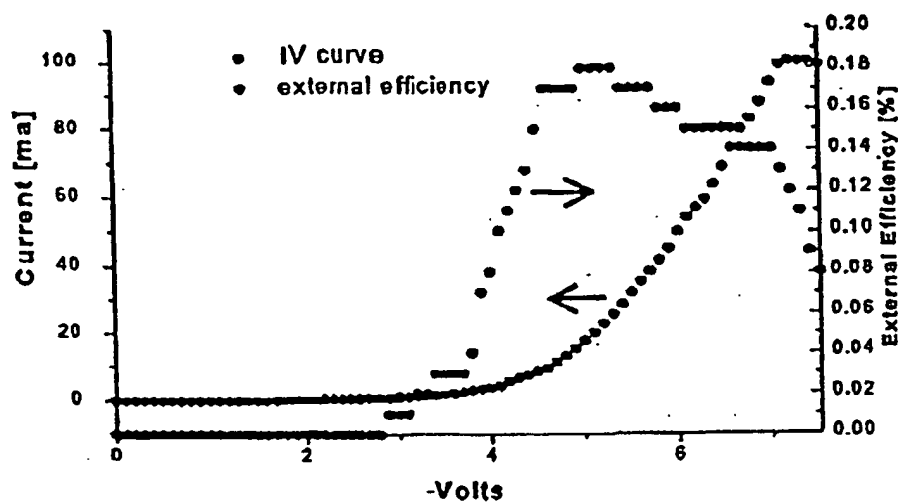


Figure 11

Resistivity/Surface Resistance

Sample	Thickness (nm)	Surface Resistance (ohm/sq)	Resistivity (ohm-cm)
Tor-CP-A1	69.9	1221	0.175
Tor-CP-A2	107	744	0.15
Tor-CP-O1	53	5546	0.596
Tor-CP-O1	104.8	1846	0.397
Tor-CP-O1	171	654	0.211
Baytron-P-1	120	158400	162.74
Baytron-P-1	314.3	75700	48.77
Baytron-P-1	592.0	22130	26.86

Tor-CP-A1	69.9	0.175
Tor-CP-A1	107	0.15
Tor-CP-O1	53	0.596
Tor-CP-O1	104.8	0.397
Tor-CP-O1	171	0.211
Baytron-P-1	120	162.74
Baytron-P-1	314.3	48.77
Baytron-P-1	592.0	26.86

Figure 12

CP Coatings on PET: Surface Resistance

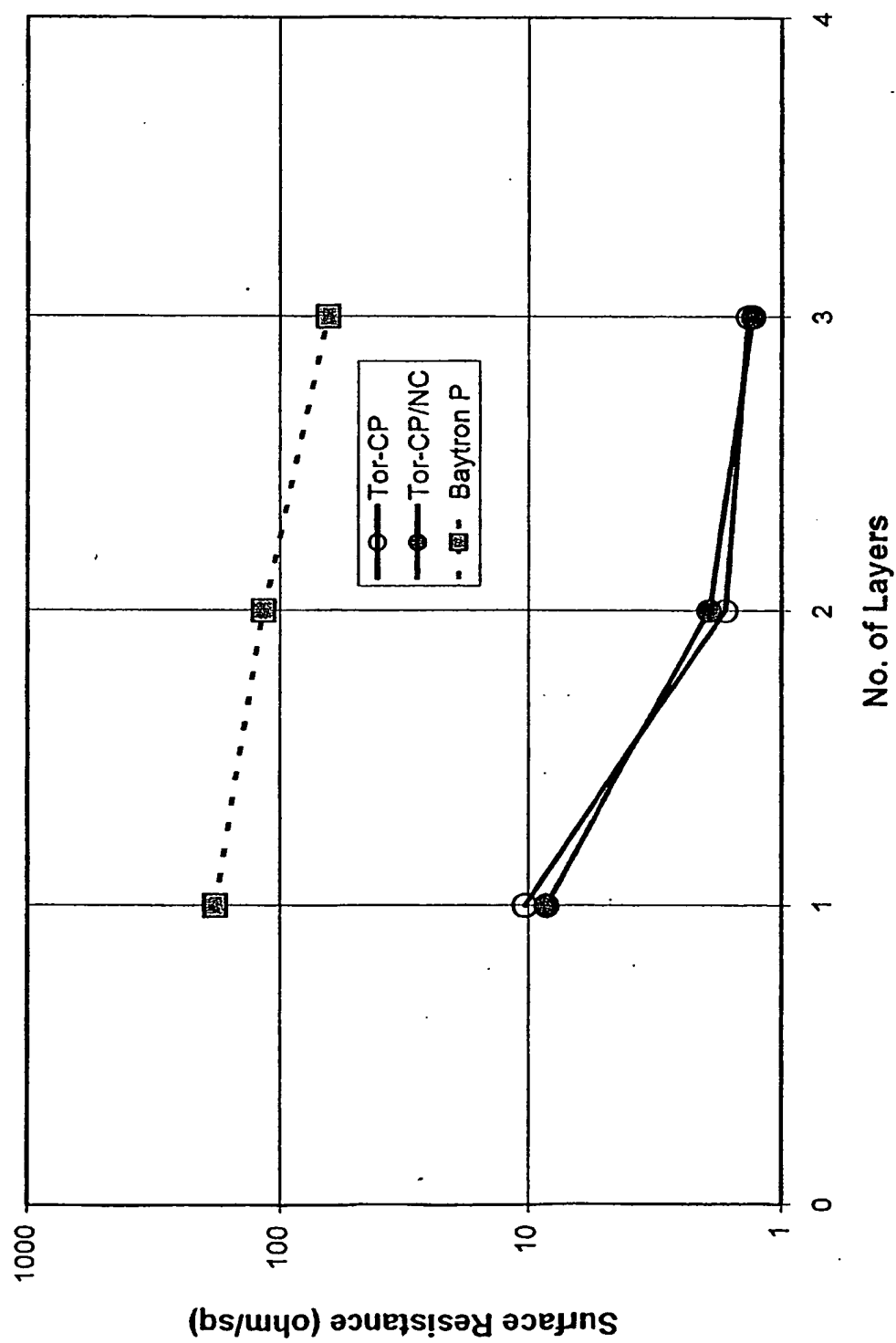


Figure 13

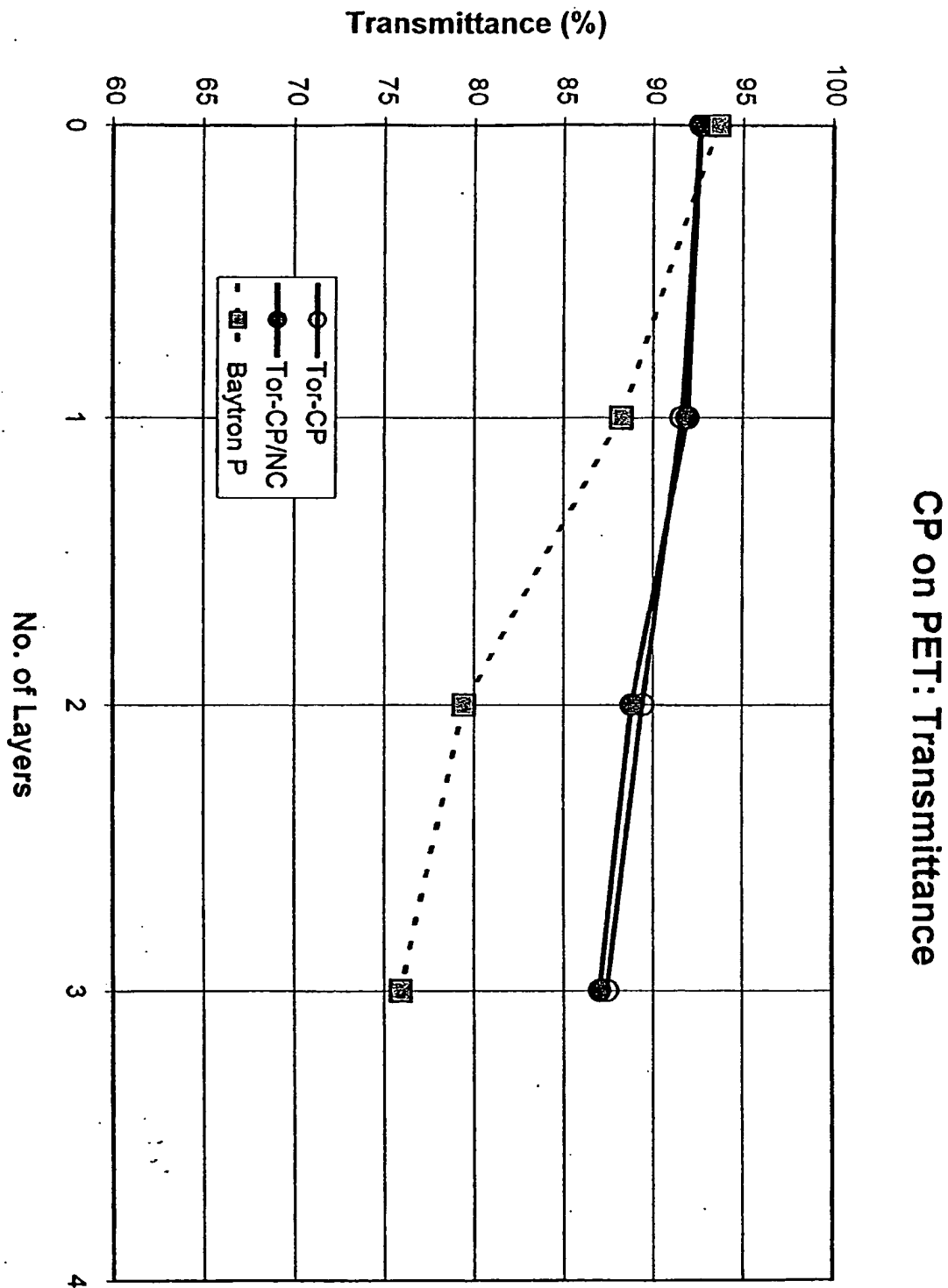


Figure 14

Layers	QZ01-72			QZ01-72 5% NC			Baytron P		
	Haze	Transmittance	Surface Resistance	Haze	Transmittance	Surface Resistance	Haze	Transmittance	Surface Resistance
0	0.93	92.6	not conductive	0.95	92.6	not conductive	0.94	93.6	not conductive
1	1.66	91.6	10.29	1.25	91.9	8.50	1.19	88.2	180
2	2.13	89.4	1.67	1.90	88.8	1.93	1.24	79.4	116
3	2.18	87.4	1.36	1.93	87.0	1.30	1.17	75.9	64

note: these samples were coated on PET (supplied by 3M)

Figure 15

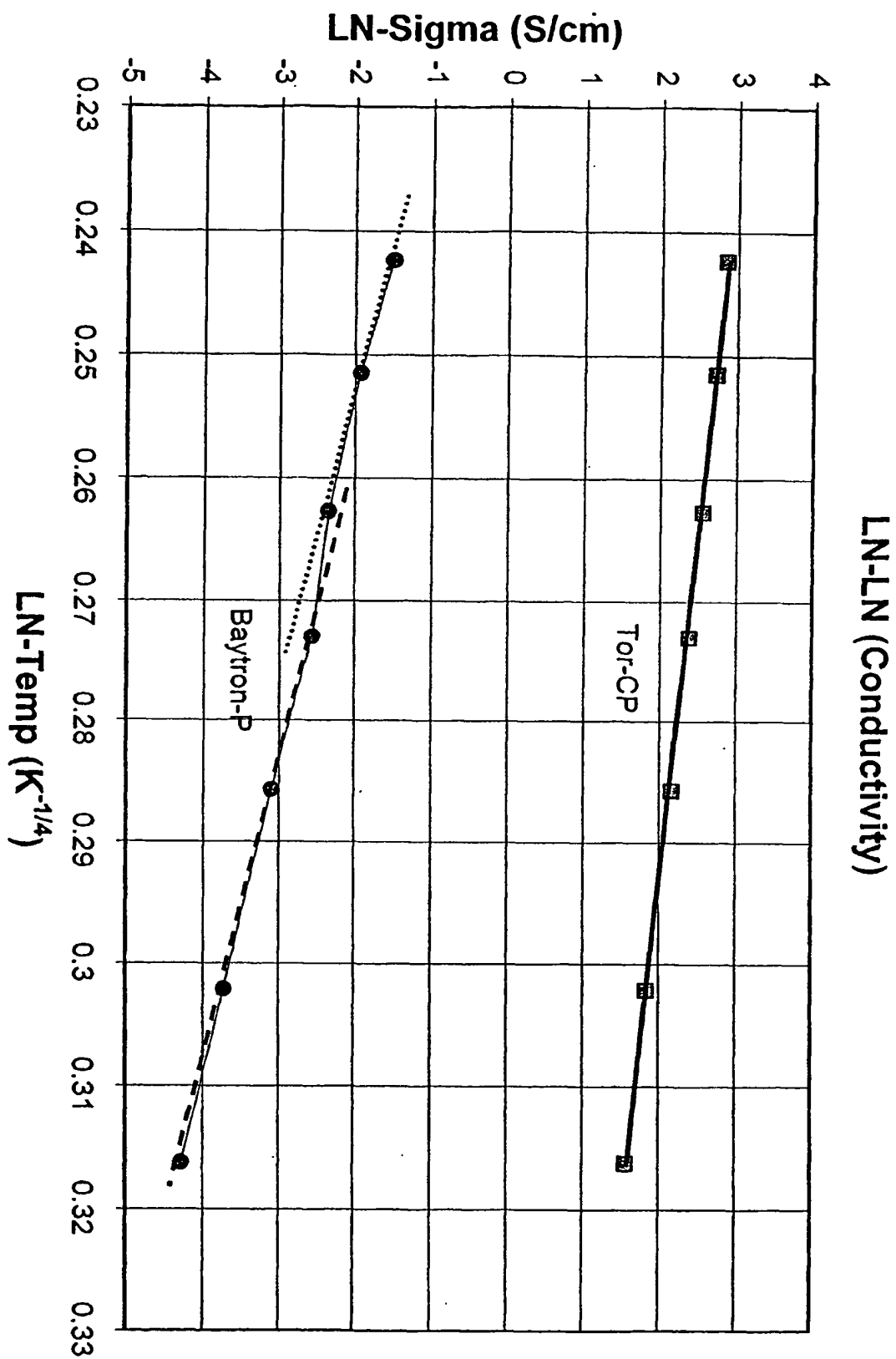


Figure 16

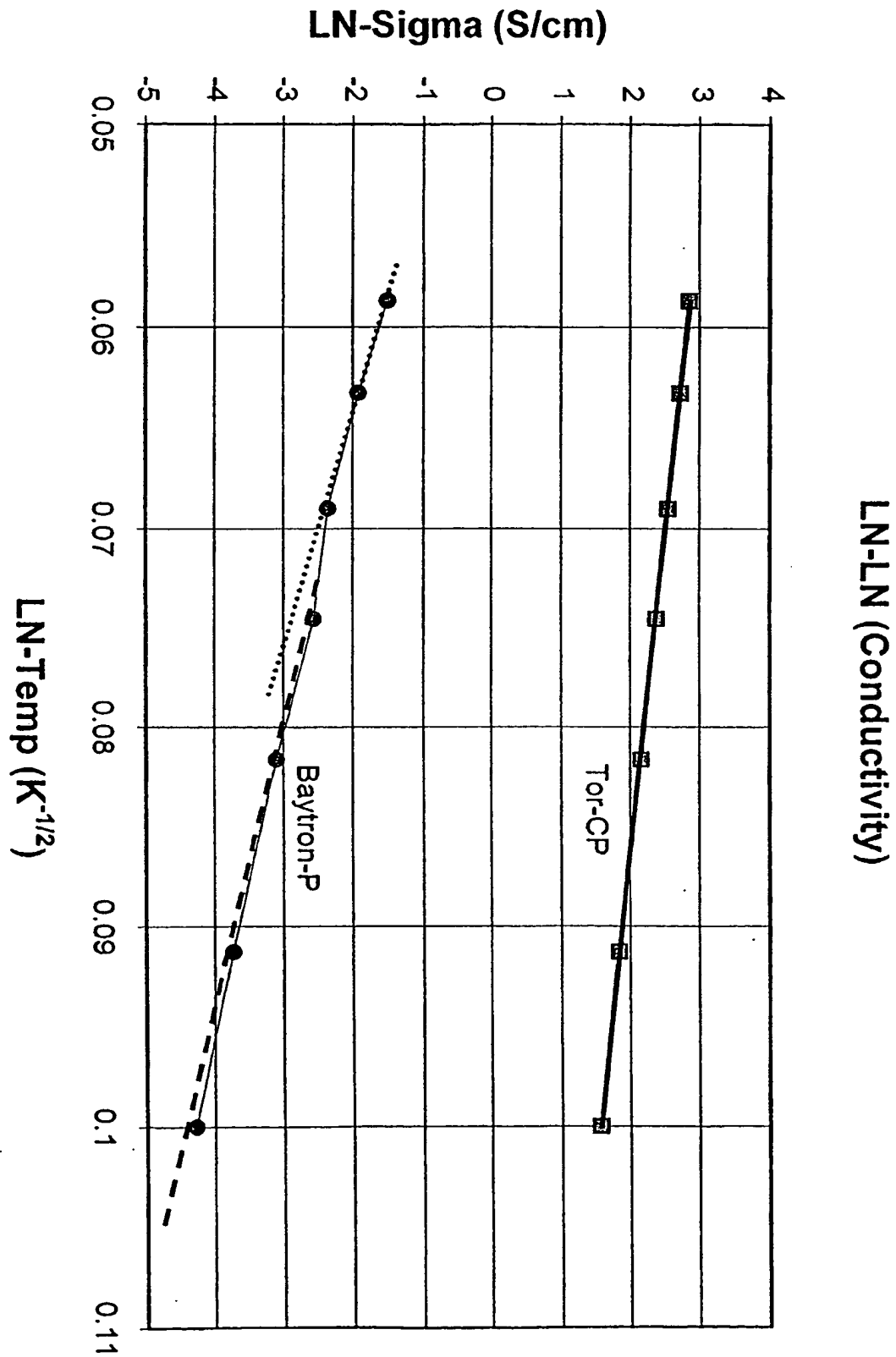


Figure 17

INTERNATIONAL SEARCH REPORT

International application No.

PCT/US02/04679

A. CLASSIFICATION OF SUBJECT MATTER

IPC(7) : H01B 1/12, 1/20; C08G 75/00; H01L 23/14

US CL : 252/500, 301.32; 528/373, 377, 378; 257/82; 340/825.82; 362/800

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

U.S. : 252/500, 301.32; 528/373, 377, 378; 257/82; 340/825.82; 362/800

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)
WEST (search terms include: polythiophene, solvent; LED, conductive)**C. DOCUMENTS CONSIDERED TO BE RELEVANT**

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X --- A	US 5,766,515 A (JONAS ET AL) 16 June 1998, see Abstract, Col 2, lines 1-16; Col 3, lines 30-35; Col 4, lines 53-57; examples 1-2.	41-43, 62-65, 117-121, 140-141 ----- 1-3, 30-34
X	US 5,998,014 A (MULLER ET AL) 7 December 1999, see Abstract; Col 2, lines 44-56; example 1.	41-43, 62-65, 117-121, 140-141
A	US 5,401,537 A (KOCHEM ET AL) 28 March 1995, see Abstract; examples.	1-3, 30-34, 41-43, 62- 65, 117-121, 140-141

☐ Further documents are listed in the continuation of Box C.☐ See patent family annex.

* Special categories of cited documents:

"A" document defining the general state of the art which is not considered to be of particular relevance

"E" earlier application or patent published on or after the international filing date

"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)

"O" document referring to an oral disclosure, use, exhibition or other means

"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art

"&" document member of the same patent family

Date of the actual completion of the international search

15 May 2002 (15.05.2002)

Date of mailing of the international search report

14 JUN 2002

Name and mailing address of the ISA/US

Commissioner of Patents and Trademarks
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Telephone No. 703 308-0661

INTERNATIONAL SEARCH REPORT

International application No.

PCT/US02/04679

Box I Observations where certain claims were found unsearchable (Continuation of Item 1 of first sheet)

This international report has not been established in respect of certain claims under Article 17(2)(a) for the following reasons:

1. ☐ Claim Nos.:
because they relate to subject matter not required to be searched by this Authority, namely:
2. ☐ Claim Nos.:
because they relate to parts of the international application that do not comply with the prescribed requirements to such an extent that no meaningful international search can be carried out, specifically:
3. ☒ Claim Nos.: 4-29, 35-40, 44-61, 66-116, 122-139, 142-146
because they are dependent claims and are not drafted in accordance with the second and third sentences of Rule 6.4(a).

Box II Observations where unity of invention is lacking (Continuation of Item 2 of first sheet)

This International Searching Authority found multiple inventions in this international application, as follows:

1. ☐ As all required additional search fees were timely paid by the applicant, this international search report covers all searchable claims.
2. ☐ As all searchable claims could be searched without effort justifying an additional fee, this Authority did not invite payment of any additional fee.
3. ☐ As only some of the required additional search fees were timely paid by the applicant, this international search report covers only those claims for which fees were paid, specifically claims Nos.:
4. ☐ No required additional search fees were timely paid by the applicant. Consequently, this international search report is restricted to the invention first mentioned in the claims; it is covered by claims Nos.:

Remark on Protest

☐
☐

The additional search fees were accompanied by the applicant's protest.

No protest accompanied the payment of additional search fees.